

超低功耗，轨到轨输出，负电源轨输入，电压反馈型 (VFB) 运算放大器

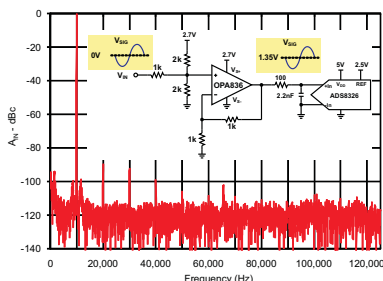
 查询样片: [OPA836](#), [OPA2836](#)

特性

- 低功耗:
 - 电源电压: **2.5V 至 5.5V**
 - 静态电流: **1mA** (典型值)
 - 断电模式: **0.5 μ A** (典型值)
- 带宽: **205MHz**
- 转换率: **560V/ μ s**
- 上升时间: **3ns** ($2V_{STEP}$)
- 稳定时间: **22ns** ($2V_{STEP}$)
- 过驱恢复时间: **60ns**
- 信噪比 (SNR): 在 **1kHz** ($1V_{RMS}$) 时为 **0.00013%** (**-117.6dBc**)
- 总谐波失真 (THD): 在 **1kHz** ($1V_{RMS}$) 时为 **0.00003%** (**-130dBc**)
- HD_2/HD_3 : **1MHz** 时 ($2V_{PP}$) 为 **-85dBc/-105dBc**
- 输入电压噪声: **4.6nV/ \sqrt{rtHz}** ($f = 100kHz$)
- 输入偏移电压: **65 μ V** (最大值为 **400 μ V**)
- 共模抑制比 (CMRR): **116dB**
- 输出驱动电流: **50mA**
- **RRO**: 轨到轨输出
- 输入电压范围: **-0.2V 至 3.9V** (**5V 电源**)
- 工作温度范围: **-40 $^{\circ}$ C 至 +125 $^{\circ}$ C**

应用范围

- 低功耗信号调节
- 音频模数转换器 (ADC) 输入缓冲器
- 低功耗逐次逼近 (SAR) 和三角积分 ($\Delta\Sigma$) 模数转换器 (ADC) 驱动器
- 便携式系统
- 低功耗系统
- 高密度系统



描述

OPA836 和 OPA2836 采用业界领先的 BiCom-3x (SiGe 互补双极型) 工艺制造, 是单通道和双通道超低功耗、轨到轨输出、负电源轨输入、电压反馈运算放大器, 专为在 2.5V 至 5.5V 的单电源范围和 $\pm 1.25V$ 至 $\pm 2.75V$ 的双电源范围内的运行而设计。每个通道的电流消耗仅为 1mA, 并具有 205MHz 的单位增益带宽, 这些放大器为轨到轨放大器设定了一个业界领先水平的功耗-性能比。

对于功耗十分重要的电池供电型便携式应用而言, OPA836 和 OPA2836 的低功耗及高频性能为设计人员提供了其他器件所无法获得的性能与功耗比。与流耗小于 1.5 μ A 的节能模式组合在一起, 此器件为电池供电应用中的高频放大器提供了一款极具吸引力的解决方案。

OPA836 和 OPA2836 提供以下封装选项:

- OPA836 单通道: 小外形尺寸晶体管 (SOT)23-6(DBV), 和具有集成增益电阻器的 10 引脚极薄四方扁平无引线 (WQFN)(RUN) 封装。
- OPA2836 双通道: 小外形尺寸集成电路 (SOIC)-8(D), 超薄型小外形尺寸 (VSSOP) (MSOP)-10(DGS), 10 引脚极薄四方扁平无引线 (WQFN) (RUN) 和 10 引脚超薄四方扁平无引线 (UQFN) (RMC) 封装。的第二段

OPA836 RUN 封装选项包括在一块印刷电路板上最小可能封装的集成增益设置电阻器 ($\approx 2mm \times 2mm$)。通过在印刷电路板 (PCB) 上添加电路迹线, 可实现 +1, -1, -1.33, +2, +2.33, -3, +4, -4, +5, -5.33, +6.33, -7, +8 的增益和 -0.1429, -0.1875, -0.25, -0.33, -0.75 的反向衰减。更多细节请参见 [应用信息](#) 部分。

该器件的特色是可在 -40 $^{\circ}$ C 至 125 $^{\circ}$ C 的扩展工业温度范围内运行。

OPA836 相关产品

描述	单通道	双通道	三通道	四通道
轨到轨	—	OPA2830	—	OPA4830
轨到轨, 低功耗	OPA835	OPA2835	—	—
轨到轨, 固定增益	OPA832	OPA2832	OPA3832	—
通用, 高转换率	OPA690	OPA2690	OPA3690	—
低噪声, 直流高精度	OPA820	OPA2822	—	OPA4820



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

PACKAGING/ORDERING INFORMATION⁽¹⁾

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.

ABSOLUTE MAXIMUM RATINGS

		UNITS
V_{S-} to V_{S+}	Supply voltage	5.5
V_I	Input voltage	$V_{S-} - 0.7V$ to $V_{S+} + 0.7V$
V_{ID}	Differential input voltage	1 V
I_I	Continuous input current	0.85 mA
I_O	Continuous output current	60 mA
	Continuous power dissipation	See Thermal Characteristics Specification
T_J	Maximum junction temperature	150°C
T_A	Operating free-air temperature range	-40°C to 125°C
T_{stg}	Storage temperature range	-65°C to 150°C
ESD ratings	HBM	6 kV
	CDM	1 kV
	MM	200 V

THERMAL INFORMATION

THERMAL METRIC ⁽¹⁾	OPA836		OPA2836				UNITS
	SOT23-6 (DBV)	WQFN-10 (RUN)	SOIC-8 (D)	VSSOP (MSOP)-10 (DGS)	WQFN-10 (RUN)	UQFN-10 (RMC)	
	6 PINS	10 PINS	8 PINS	10 PINS	10 PINS	10 PINS	
θ_{JA} Junction-to-ambient thermal resistance	194	145.8	150.1	206	145.8	143.2	°C/W
θ_{JcTop} Junction-to-case (top) thermal resistance	129.2	75.1	83.8	75.3	75.1	49.0	
θ_{JB} Junction-to-board thermal resistance	39.4	38.9	68.4	96.2	38.9	61.9	
ψ_{JT} Junction-to-top characterization parameter	25.6	13.5	33.0	12.9	13.5	3.3	
ψ_{JB} Junction-to-board characterization parameter	38.9	104.5	67.9	94.6	104.5	61.9	
θ_{JcBot} Junction-to-case (bottom) thermal resistance	n/a	n/a	n/a	n/a	n/a	n/a	

(1) 有关传统和全新热度的更多信息，请参阅 IC 封装热量应用报告（文献号：ZHCA543）。

SPECIFICATIONS: $V_S = 2.7\text{ V}$

Test conditions unless otherwise noted: $V_{S+} = +2.7\text{ V}$, $V_{S-} = 0\text{ V}$, $V_{OUT} = 1\text{ V}_{PP}$, $R_F = 0\ \Omega$, $R_L = 1\text{ k}\Omega$, $G = 1\text{ V/V}$, Input and Output Referenced to mid-supply. $T_A = 25^\circ\text{C}$. Unless otherwise noted

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	TEST LEVEL ⁽¹⁾	
AC PERFORMANCE							
Small-signal bandwidth	$V_{OUT} = 100\text{ mV}_{PP}$, $G = 1$		200		MHz	C	
	$V_{OUT} = 100\text{ mV}_{PP}$, $G = 2$		100				
	$V_{OUT} = 100\text{ mV}_{PP}$, $G = 5$		26				
	$V_{OUT} = 100\text{ mV}_{PP}$, $G = 10$		11				
Gain-bandwidth product	$V_{OUT} = 100\text{ mV}_{PP}$, $G = 10$		110		MHz	C	
Large-signal bandwidth	$V_{OUT} = 1\text{ V}_{PP}$, $G = 2$		60		MHz	C	
Bandwidth for 0.1dB flatness	$V_{OUT} = 1\text{ V}_{PP}$, $G=2$		25		MHz	C	
Slew rate, Rise/Fall	$V_{OUT} = 1V_{STEP}$, $G = 2$		260/240		V/ μ s	C	
Rise/Fall time			4/4.5		ns	C	
Settling time to 1%, Rise/Fall			15/15		ns	C	
Settling time to 0.1%, Rise/Fall			30/25		ns	C	
Settling time to 0.01%, Rise/Fall			50/45		ns	C	
Overshoot/Undershoot				5/3		%	C
2 nd Order Harmonic Distortion		$f = 10\text{ kHz}$, $V_{IN_CM} = \text{mid-supply} - 0.5\text{ V}$		-133		dBc	C
	$f = 100\text{ kHz}$, $V_{IN_CM} = \text{mid-supply} - 0.5\text{ V}$		-120		C		
	$f = 1\text{ MHz}$, $V_{IN_CM} = \text{mid-supply} - 0.5\text{ V}$		-84		C		
3 rd Order Harmonic Distortion	$f = 10\text{ kHz}$, $V_{IN_CM} = \text{mid-supply} - 0.5\text{ V}$		-137		dBc	C	
	$f = 100\text{ kHz}$, $V_{IN_CM} = \text{mid-supply} - 0.5\text{ V}$		-130			C	
	$f = 1\text{ MHz}$, $V_{IN_CM} = \text{mid-supply} - 0.5\text{ V}$		-105			C	
2 nd Order Intermodulation Distortion	$f = 1\text{ MHz}$, 200 kHz Tone Spacing, V_{OUT} Envelope = $1V_{PP}$, $V_{IN_CM} = \text{mid-supply} - 0.5\text{ V}$		-90		dBc	C	
3 rd Order Intermodulation Distortion	$f = 1\text{ MHz}$, 200 kHz Tone Spacing, V_{OUT} Envelope = $1V_{PP}$, $V_{IN_CM} = \text{mid-supply} - 0.5\text{ V}$		-90		dBc	C	
Input voltage noise	$f = 100\text{ KHz}$		4.6		nV/ $\sqrt{\text{Hz}}$	C	
Voltage Noise 1/f corner frequency			215		Hz	C	
Input current noise	$f = 1\text{ MHz}$		0.75		pA/ $\sqrt{\text{Hz}}$	C	
Current Noise 1/f corner frequency			31.7		kHz	C	
Overdrive recovery time, Over/Under	Overdrive = 0.5 V		55/60		ns	C	
Closed-loop output impedance	$f = 100\text{ kHz}$		0.02		Ω	C	
Channel to channel crosstalk (OPA2836)	$f = 10\text{ kHz}$		-120		dB	C	

(1) Test levels (all values set by characterization and simulation): **(A)** 100% tested at 25°C; over temperature limits by characterization and simulation. **(B)** Not tested in production; limits set by characterization and simulation. **(C)** Typical value only for information.

SPECIFICATIONS: $V_S = 2.7\text{ V}$

Test conditions unless otherwise noted: $V_{S+} = +2.7\text{ V}$, $V_{S-} = 0\text{ V}$, $V_{OUT} = 1\text{ V}_{PP}$, $R_F = 0\ \Omega$, $R_L = 1\text{ k}\Omega$, $G = 1\text{ V/V}$, Input and Output Referenced to mid-supply. $T_A = 25^\circ\text{C}$. Unless otherwise noted

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	TEST LEVEL ⁽¹⁾
DC PERFORMANCE						
Open-loop voltage gain (A_{OL})		100	125		dB	A
Input referred offset voltage	$T_A = 25^\circ\text{C}$		± 65	± 400	μV	A
	$T_A = 0^\circ\text{C}$ to 70°C			± 680		B
	$T_A = -40^\circ\text{C}$ to 85°C			± 760		
	$T_A = -40^\circ\text{C}$ to 125°C			± 1060		
Input offset voltage drift ⁽²⁾	$T_A = 0^\circ\text{C}$ to 70°C		± 1	± 6.2	$\mu\text{V}/^\circ\text{C}$	B
	$T_A = -40^\circ\text{C}$ to 85°C		± 1	± 6		
	$T_A = -40^\circ\text{C}$ to 125°C		± 1.1	± 6.6		
Input bias current	$T_A = 25^\circ\text{C}$	300	650	1000	nA	A
	$T_A = 0^\circ\text{C}$ to 70°C	190		1400		B
	$T_A = -40^\circ\text{C}$ to 85°C	120		1500		
	$T_A = -40^\circ\text{C}$ to 125°C	120		1800		
Input bias current drift ⁽²⁾	$T_A = 0^\circ\text{C}$ to 70°C		± 0.33	± 2	nA/ $^\circ\text{C}$	B
	$T_A = -40^\circ\text{C}$ to 85°C		± 0.32	± 1.9		
	$T_A = -40^\circ\text{C}$ to 125°C		± 0.37	± 2.1		
Input offset current	$T_A = 25^\circ\text{C}$		± 30	± 180	nA	A
	$T_A = 0^\circ\text{C}$ to 70°C		± 30	± 200		B
	$T_A = -40^\circ\text{C}$ to 85°C		± 30	± 215		
	$T_A = -40^\circ\text{C}$ to 125°C		± 30	± 240		
Input offset current drift ⁽²⁾	$T_A = 0^\circ\text{C}$ to 70°C		± 77	± 460	pA/ $^\circ\text{C}$	B
	$T_A = -40^\circ\text{C}$ to 85°C		± 95	± 575		
	$T_A = -40^\circ\text{C}$ to 125°C		± 100	± 600		
INPUT						
Common-mode input range low	$T_A = 25^\circ\text{C}$, <3dB degradation in CMRR limit		-0.2	0	V	A
	$T_A = -40^\circ\text{C}$ to 125°C , <3dB degradation in CMRR limit		-0.2	0	V	B
Common-mode input range high	$T_A = 25^\circ\text{C}$, <3dB degradation in CMRR limit	1.5	1.6		V	A
	$T_A = -40^\circ\text{C}$ to 125°C , <3dB degradation in CMRR limit	1.5	1.6		V	B
Input linear operating voltage range	$T_A = 25^\circ\text{C}$, <6dB degradation in THD		-0.3 to 1.75		V	C
Common-mode rejection ratio		91	114		dB	A
Input impedance common mode			200 1.2		k Ω pF	C
Input impedance differential mode			200 1		k Ω pF	C
OUTPUT						
Linear output voltage low	$T_A = 25^\circ\text{C}$, $G = 5$		0.15	0.2	V	A
	$T_A = -40^\circ\text{C}$ to 125°C , $G = 5$		0.15	0.2	V	B
Linear output voltage high	$T_A = 25^\circ\text{C}$, $G = 5$	2.45	2.5		V	A
	$T_A = -40^\circ\text{C}$ to 125°C , $G = 5$	2.45	2.5		V	B
Output saturation voltage, High / Low	$T_A = 25^\circ\text{C}$, $G = 5$		80/40		mV	C
Linear output current drive	$T_A = 25^\circ\text{C}$	± 40	± 45		mA	A
	$T_A = -40^\circ\text{C}$ to 125°C	± 40	± 45		mA	B

- (1) Test levels (all values set by characterization and simulation): **(A)** 100% tested at 25°C ; over temperature limits by characterization and simulation. **(B)** Not tested in production; limits set by characterization and simulation. **(C)** Typical value only for information.
- (2) Input Offset Voltage Drift, Input Bias Current Drift, and Input Offset Current Drift are average values calculated by taking data at the end points, computing the difference, and dividing by the temperature range.

SPECIFICATIONS: $V_S = 2.7\text{ V}$ (continued)

Test conditions unless otherwise noted: $V_{S+} = +2.7\text{ V}$, $V_{S-} = 0\text{ V}$, $V_{OUT} = 1\text{ V}_{PP}$, $R_F = 0\ \Omega$, $R_L = 1\text{ k}\Omega$, $G = 1\text{ V/V}$, Input and Output Referenced to mid-supply. $T_A = 25^\circ\text{C}$. Unless otherwise noted

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	TEST LEVEL ⁽¹⁾
GAIN SETTING RESISTORS (OPA836IRUN ONLY)						
Resistor FB1 to FB2	DC resistance	1584	1600	1616	Ω	A
Resistor FB2 to FB3	DC resistance	1188	1200	1212	Ω	A
Resistor FB3 to FB4	DC resistance	396	400	404	Ω	A
Resistor Tolerance	DC resistance			± 1	%	A
Resistor Temperature Coefficient	DC resistance		<10		PPM	C
POWER SUPPLY						
Specified operating voltage		2.5		5.5	V	B
Quiescent operating current per amplifier	$T_A = 25^\circ\text{C}$	0.7	0.95	1.15	mA	A
	$T_A = -40^\circ\text{C}$ to 125°C	0.6		1.4	mA	B
Power supply rejection ($\pm\text{PSRR}$)		91	108		dB	A
POWER DOWN						
Enable voltage threshold	Specified "on" above $V_S + 2.1\text{ V}$			2.1	V	A
Disable voltage threshold	Specified "off" below $V_S + 0.7\text{ V}$	0.7			V	A
Powerdown pin bias current	$\overline{\text{PD}} = 0.5\text{ V}$		20	500	nA	A
Powerdown quiescent current	$\overline{\text{PD}} = 0.5\text{ V}$		0.5	1.5	μA	A
Turn-on time delay	Time from $\overline{\text{PD}} = \text{high}$ to $V_{OUT} = 90\%$ of final value		200		ns	C
Turn-off time delay	Time from $\overline{\text{PD}} = \text{low}$ to $V_{OUT} = 10\%$ of original value		25		ns	C

SPECIFICATIONS: $V_S = 5\text{ V}$

Test conditions unless otherwise noted: $V_{S+} = +5\text{ V}$, $V_{S-} = 0\text{ V}$, $V_{OUT} = 2\text{ V}_{PP}$, $R_F = 0\ \Omega$, $R_L = 1\text{ k}\Omega$, $G = 1\text{ V/V}$, Input and Output Referenced to mid-supply. $T_A = 25^\circ\text{C}$. Unless otherwise noted.

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	TEST LEVEL ⁽¹⁾	
AC PERFORMANCE							
Small-signal bandwidth	$V_{OUT} = 100\text{ mV}_{PP}$, $G = 1$		205		MHz	C	
	$V_{OUT} = 100\text{ mV}_{PP}$, $G = 2$		100				
	$V_{OUT} = 100\text{ mV}_{PP}$, $G = 5$		28				
	$V_{OUT} = 100\text{ mV}_{PP}$, $G = 10$		11.8				
Gain-bandwidth product	$V_{OUT} = 100\text{ mV}_{PP}$, $G = 10$		118		MHz	C	
Large-signal bandwidth	$V_{OUT} = 2\text{ V}_{PP}$, $G = 2$		87		MHz	C	
Bandwidth for 0.1dB flatness	$V_{OUT} = 2\text{ V}_{PP}$, $G = 2$		29		MHz	C	
Slew rate, Rise/Fall	$V_{OUT} = 2\text{ V Step}$, $G = 2$		560/580		V/ μs	C	
Rise/Fall time			3/3		ns	C	
Settling time to 1%, Rise/Fall			22/22		ns	C	
Settling time to 0.1%, Rise/Fall			30/30		ns	C	
Settling time to 0.01%, Rise/Fall			40/45		ns	C	
Overshoot/Undershoot				7.5/5		%	C
2 nd Order Harmonic Distortion		$f = 10\text{ kHz}$		-133		dBc	C
	$f = 100\text{ kHz}$		-120		C		
	$f = 1\text{ MHz}$		-85		C		
3 rd Order Harmonic Distortion	$f = 10\text{ kHz}$		-140		dBc	C	
	$f = 100\text{ kHz}$		-130			C	
	$f = 1\text{ MHz}$		-105			C	
2 nd Order Intermodulation Distortion	$f = 1\text{ MHz}$, 200 kHz Tone Spacing, $V_{OUT}\text{ Envelope} = 2\text{ V}_{PP}$		-79		dBc	C	
3 rd Order Intermodulation Distortion			-91				
Signal to Noise Ratio, SNR	$f = 1\text{ kHz}$, $V_{OUT} = 1\text{ V}_{RMS}$, 22kHz bandwidth		0.00013		%	C	
			-117.6		dBc	C	
Total Harmonic Distortion, THD	$f = 1\text{ kHz}$, $V_{OUT} = 1\text{ V}_{RMS}$		0.00003		%	C	
			-130		dBc	C	
Input voltage noise	$f = 100\text{ KHz}$		4.6		nV/ $\sqrt{\text{Hz}}$	C	
Voltage Noise 1/f corner frequency			215		Hz	C	
Input current noise	$f > 1\text{ MHz}$		0.75		pA/ $\sqrt{\text{Hz}}$	C	
Current Noise 1/f corner frequency			31.7		kHz	C	
Overdrive recovery time, Over/Under	Overdrive = 0.5 V		55/60		ns	C	
Closed-loop output impedance	$f = 100\text{ kHz}$		0.02		Ω	C	
Channel to channel crosstalk (OPA2836)	$f = 10\text{ kHz}$		-120		dB	C	

(1) Test levels (all values set by characterization and simulation): **(A)** 100% tested at 25°C; over temperature limits by characterization and simulation. **(B)** Not tested in production; limits set by characterization and simulation. **(C)** Typical value only for information.

SPECIFICATIONS: $V_S = 5\text{ V}$

Test conditions unless otherwise noted: $V_{S+} = +5\text{ V}$, $V_{S-} = 0\text{ V}$, $V_{OUT} = 2\text{ V}_{PP}$, $R_F = 0\ \Omega$, $R_L = 1\text{ k}\Omega$, $G = 1\text{ V/V}$, Input and Output Referenced to mid-supply. $T_A = 25^\circ\text{C}$. Unless otherwise noted.

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	TEST LEVEL ⁽¹⁾
DC PERFORMANCE						
Open-loop voltage gain (A_{OL})		100	122		dB	A
Input referred offset voltage	$T_A = 25^\circ\text{C}$		± 65	± 400	μV	A
	$T_A = 0^\circ\text{C}$ to 70°C			± 685		B
	$T_A = -40^\circ\text{C}$ to 85°C			± 765		
	$T_A = -40^\circ\text{C}$ to 125°C			± 1080		
Input offset voltage drift ⁽²⁾	$T_A = 0^\circ\text{C}$ to 70°C		± 1.05	± 6.3	$\mu\text{V}/^\circ\text{C}$	B
	$T_A = -40^\circ\text{C}$ to 85°C		± 1	± 6.1		
	$T_A = -40^\circ\text{C}$ to 125°C		± 1.1	± 6.8		
Input bias current	$T_A = 25^\circ\text{C}$	300	650	1000	nA	A
	$T_A = 0^\circ\text{C}$ to 70°C	190		1400		B
	$T_A = -40^\circ\text{C}$ to 85°C	120		1550		
	$T_A = -40^\circ\text{C}$ to 125°C	120		1850		
Input bias current drift ⁽²⁾	$T_A = 0^\circ\text{C}$ to 70°C		± 0.34	± 2	nA/ $^\circ\text{C}$	B
	$T_A = -40^\circ\text{C}$ to 85°C		± 0.34	± 2		
	$T_A = -40^\circ\text{C}$ to 125°C		± 0.38	± 2.3		
Input offset current	$T_A = 25^\circ\text{C}$		± 30	± 180	nA	A
	$T_A = 0^\circ\text{C}$ to 70°C		± 30	± 200		B
	$T_A = -40^\circ\text{C}$ to 85°C		± 30	± 215		
	$T_A = -40^\circ\text{C}$ to 125°C		± 30	± 250		
Input offset current drift ⁽²⁾	$T_A = 0^\circ\text{C}$ to 70°C		± 80	± 480	pA/ $^\circ\text{C}$	B
	$T_A = -40^\circ\text{C}$ to 85°C		± 100	± 600		
	$T_A = -40^\circ\text{C}$ to 125°C		± 110	± 660		
INPUT						
Common-mode input range low	$T_A = 25^\circ\text{C}$, <3dB degradation in CMRR limit		-0.2	0	V	A
	$T_A = -40^\circ\text{C}$ to 125°C , <3dB degradation in CMRR limit		-0.2	0	V	B
Common-mode input range high	$T_A = 25^\circ\text{C}$, <3dB degradation in CMRR limit	3.8	3.9		V	A
	$T_A = -40^\circ\text{C}$ to 125°C , <3dB degradation in CMRR limit	3.8	3.9		V	B
Input linear operating voltage range	$T_A = 25^\circ\text{C}$, <6dB degradation in THD		-0.3 to 4.05		V	C
Common-mode rejection ratio		94	116		dB	A
Input impedance common mode			200 1.2		k Ω pF	C
Input impedance differential mode			200 1		k Ω pF	C
OUTPUT						
Linear output voltage low	$T_A = 25^\circ\text{C}$, $G =$		0.15	0.2	V	A
	$T_A = -40^\circ\text{C}$ to 125°C , $G = 5$		0.15	0.2	V	B
Linear output voltage high	$T_A = 25^\circ\text{C}$, $G = 5$	4.75	4.8		V	A
	$T_A = -40^\circ\text{C}$ to 125°C , $G = 5$	4.75	4.8		V	B
Output saturation voltage, High / Low	$T_A = 25^\circ\text{C}$, $G = 5$		100/50		mV	C
Linear output current drive	$T_A = 25^\circ\text{C}$	± 40	± 50		mA	A
	$T_A = -40^\circ\text{C}$ to 125°C	± 40	± 50		mA	B

- (1) Test levels (all values set by characterization and simulation): **(A)** 100% tested at 25°C ; over temperature limits by characterization and simulation. **(B)** Not tested in production; limits set by characterization and simulation. **(C)** Typical value only for information.
- (2) Input Offset Voltage Drift, Input Bias Current Drift, and Input Offset Current Drift are average values calculated by taking data at the end points, computing the difference, and dividing by the temperature range.

SPECIFICATIONS: $V_S = 5\text{ V}$ (continued)

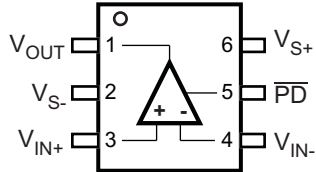
Test conditions unless otherwise noted: $V_{S+} = +5\text{ V}$, $V_{S-} = 0\text{ V}$, $V_{OUT} = 2\text{ V}_{PP}$, $R_F = 0\ \Omega$, $R_L = 1\text{ k}\Omega$, $G = 1\text{ V/V}$, Input and Output Referenced to mid-supply. $T_A = 25^\circ\text{C}$. Unless otherwise noted.

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	TEST LEVEL ⁽¹⁾
GAIN SETTING RESISTORS (OPA836IRUN ONLY)						
Resistor FB1 to FB2	DC resistance	1584	1600	1616	Ω	A
Resistor FB2 to FB3	DC resistance	1188	1200	1212	Ω	A
Resistor FB3 to FB4	DC resistance	396	400	404	Ω	A
Resistor Tolerance	DC resistance			± 1	%	A
Resistor Temperature Coefficient	DC resistance		<10		PPM	C
POWER SUPPLY						
Specified operating voltage		2.5		5.5	V	B
Quiescent operating current per amplifier	$T_A = 25^\circ\text{C}$	0.8	1.0	1.2	mA	A
	$T_A = -40^\circ\text{C}$ to 125°C	0.65		1.5	mA	B
Power supply rejection ($\pm\text{PSRR}$)		94	108		dB	A
POWER DOWN						
Enable voltage threshold	Specified "on" above $V_{S-} + 2.1\text{ V}$			2.1	V	A
Disable voltage threshold	Specified "off" below $V_{S-} + 0.7\text{ V}$	0.7			V	A
Powerdown pin bias current	$\overline{\text{PD}} = 0.5\text{ V}$		20	500	nA	A
Powerdown quiescent current	$\overline{\text{PD}} = 0.5\text{ V}$		0.5	1.5	μA	A
Turn-on time delay	Time from $\overline{\text{PD}} = \text{high}$ to $V_{OUT} = 90\%$ of final value		170		ns	C
Turn-off time delay	Time from $\overline{\text{PD}} = \text{low}$ to $V_{OUT} = 10\%$ of original value		35		ns	C

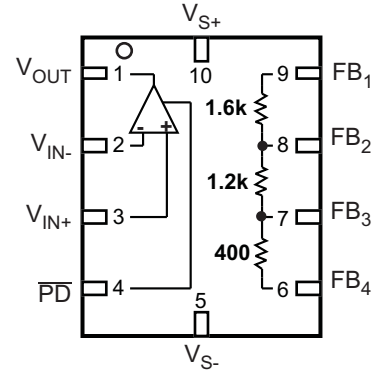
DEVICE INFORMATION

PIN CONFIGURATIONS

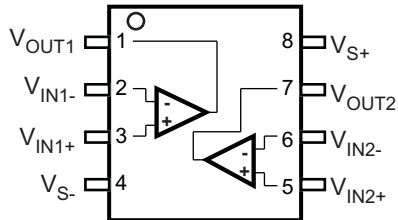
OPA836 (TOP VIEW)
SOT23-6 (DBV)



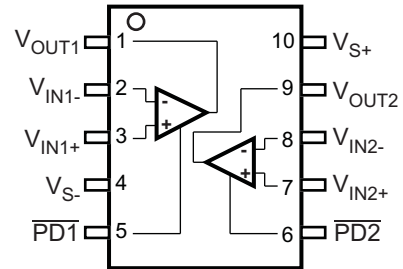
OPA836 (TOP VIEW)
WQFN-10 (RUN)



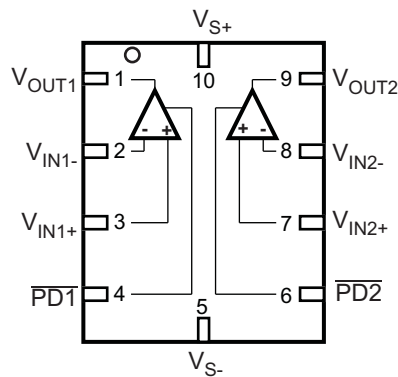
OPA2836 (TOP VIEW)
SOIC-8 (D)



OPA2836 (TOP VIEW)
VSSOP (MSOP)-10 (DGS)



OPA2836 (TOP VIEW)
WQFN-10 (RUN), UQFN-10 (RMC)



PIN FUNCTIONS

PIN		DESCRIPTION
NUMBER	NAME	
OPA836 DBV PACKAGE		
1	V _{OUT}	Amplifier output
2	V _{S-}	Negative power supply input
3	V _{IN+}	Amplifier non-inverting input
4	V _{IN-}	Amplifier inverting input
5	\overline{PD}	Amplifier Power Down, low = low power mode, high = normal operation (PIN MUST BE DRIVEN)
6	V _{S+}	Positive power supply input
OPA836 RUN PACKAGE		
1	V _{OUT}	Amplifier output
2	V _{IN-}	Amplifier inverting input
3	V _{IN+}	Amplifier non-inverting input
4	\overline{PD}	Amplifier Power Down, low = low power mode, high = normal operation (PIN MUST BE DRIVEN)
5	V _{S-}	Negative power supply input
6	FB ₄	Connection to bottom of 250 Ω internal gain setting resistors
7	FB ₃	Connection to junction of 750 and 250 Ω internal gain setting resistors
8	FB ₂	Connection to junction of 1k and 750 Ω internal gain setting resistors
9	FB ₁	Connection to top of 1kΩ internal gain setting resistors
10	V _{S+}	Positive power supply input
OPA2836 D PACKAGE		
1	V _{OUT1}	Amplifier 1 output
2	V _{IN1-}	Amplifier 1 inverting input
3	V _{IN1+}	Amplifier 1 non-inverting input
4	V _{S-}	Negative power supply input
5	V _{IN2+}	Amplifier 2 non-inverting input
6	V _{IN2-}	Amplifier 2 inverting input
7	V _{OUT2}	Amplifier 2 output
8	V _{S+}	Positive power supply input
OPA2836 DSG PACKAGE		
1	V _{OUT1}	Amplifier 1 output
2	V _{IN1-}	Amplifier 1 inverting input
3	V _{IN1+}	Amplifier 1 non-inverting input
4	V _{S-}	Negative power supply input
5	$\overline{PD1}$	Amplifier 1 Power Down, low = low power mode, high = normal operation (PIN MUST BE DRIVEN)
6	$\overline{PD2}$	Amplifier 2 Power Down, low = low power mode, high = normal operation (PIN MUST BE DRIVEN)
7	V _{IN2+}	Amplifier 2 non-inverting input
8	V _{IN2-}	Amplifier 2 inverting input
9	V _{OUT2}	Amplifier 2 output
10	V _{S+}	Positive power supply input

PIN FUNCTIONS (continued)

PIN		DESCRIPTION
NUMBER	NAME	
OPA2836 RUN AND RMC PACKAGES		
1	V_{OUT1}	Amplifier 1 output
2	V_{IN1-}	Amplifier 1 inverting input
3	V_{IN1+}	Amplifier 1 non-inverting input
4	$\overline{PD1}$	Amplifier 1 Power Down, low = low power mode, high = normal operation (PIN MUST BE DRIVEN)
5	V_{S-}	Negative power supply input
6	$\overline{PD2}$	Amplifier 2 Power Down, low = low power mode, high = normal operation (PIN MUST BE DRIVEN)
7	V_{IN2+}	Amplifier 2 non-inverting input
8	V_{IN2-}	Amplifier 2 inverting input
9	V_{OUT2}	Amplifier 2 output
10	V_{S+}	Positive power supply input

TYPICAL PERFORMANCE GRAPHS: $V_S = 2.7\text{ V}$

Test conditions unless otherwise noted: $V_{S+} = +2.7\text{ V}$, $V_{S-} = 0\text{ V}$, $V_{OUT} = 1\text{ V}_{PP}$, $R_F = 0\ \Omega$, $R_L = 1\text{ k}\Omega$, $G = 1\text{ V/V}$, Input and Output Referenced to mid-supply unless otherwise noted. $T_A = 25^\circ\text{C}$.

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Input Offset Current	vs Free-Air Temperature	Figure 25
Input Offset Current Drift		Figure 26

TYPICAL PERFORMANCE GRAPHS: $V_S = 2.7\text{ V}$

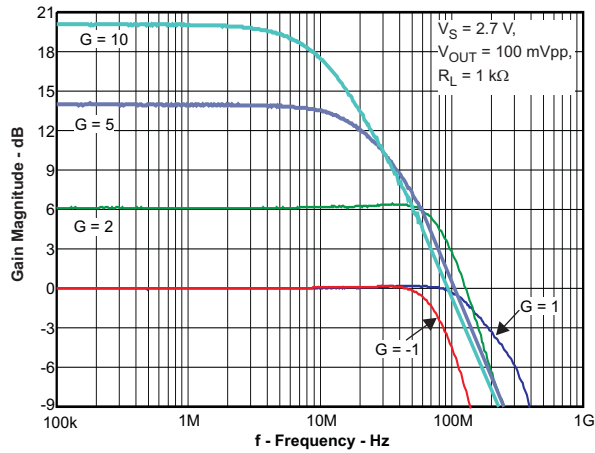


Figure 1. Small Signal Frequency Response

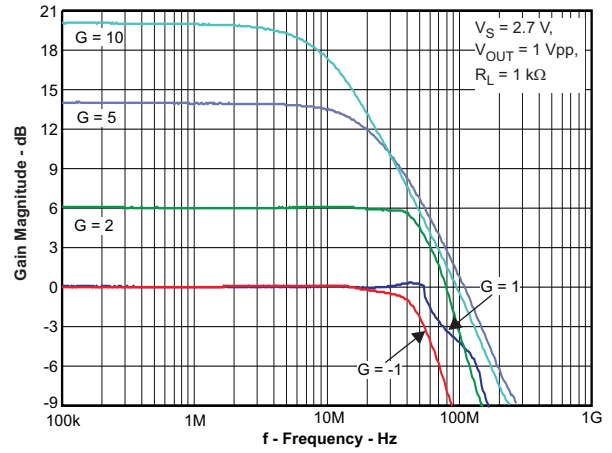


Figure 2. Large Signal Frequency Response

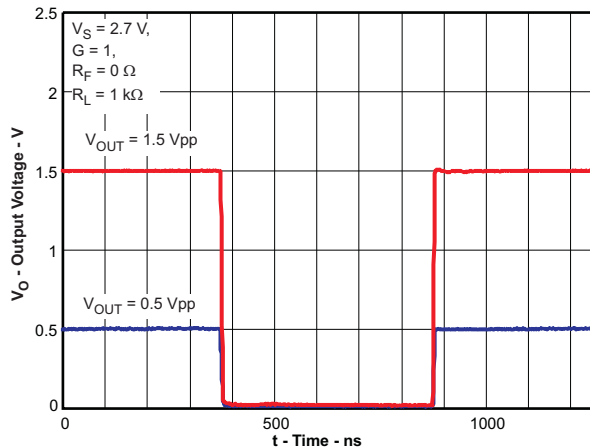


Figure 3. Noninverting Pulse Response

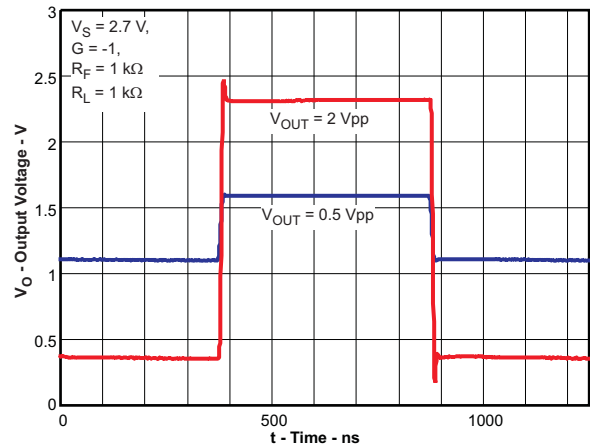


Figure 4. Inverting Pulse Response

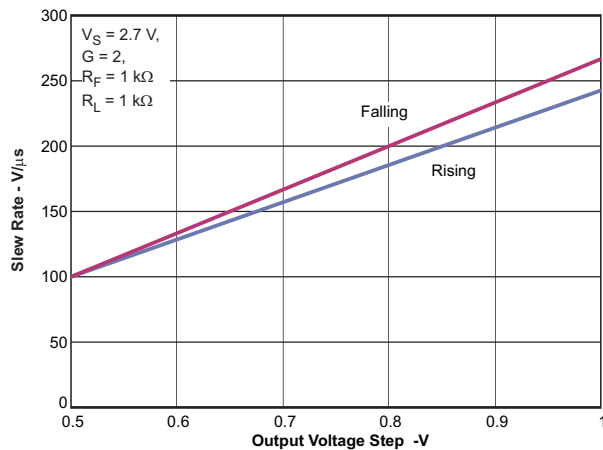


Figure 5. Slew Rate vs Output Voltage Step

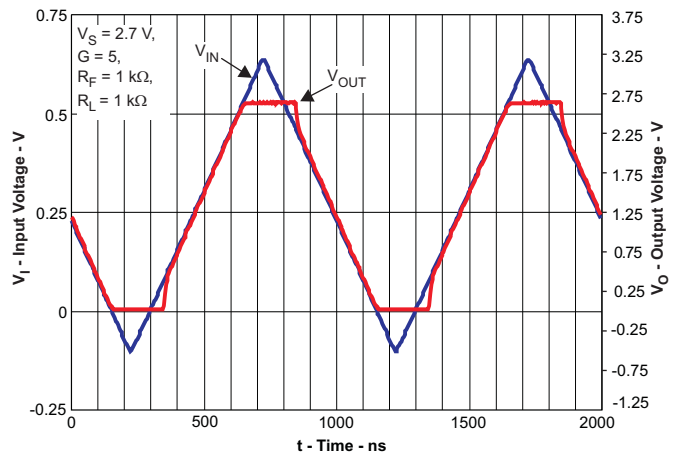


Figure 6. Output Overdrive Recovery

TYPICAL PERFORMANCE GRAPHS: $V_S = 2.7\text{ V}$ (continued)

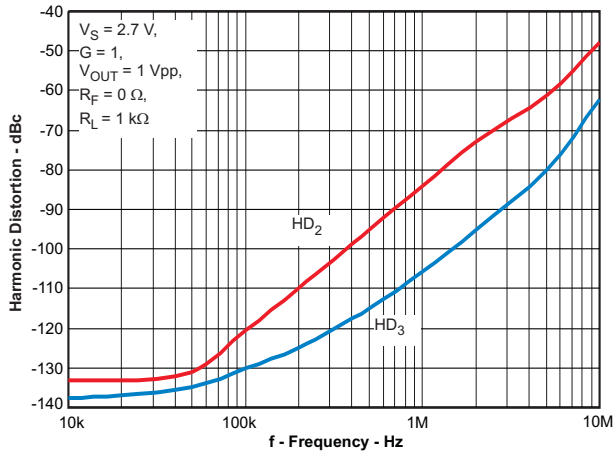


Figure 7. Harmonic Distortion vs Frequency

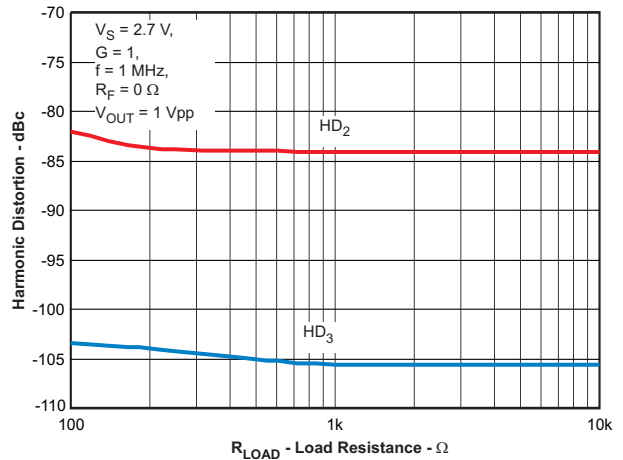


Figure 8. Harmonic Distortion vs Load Resistance

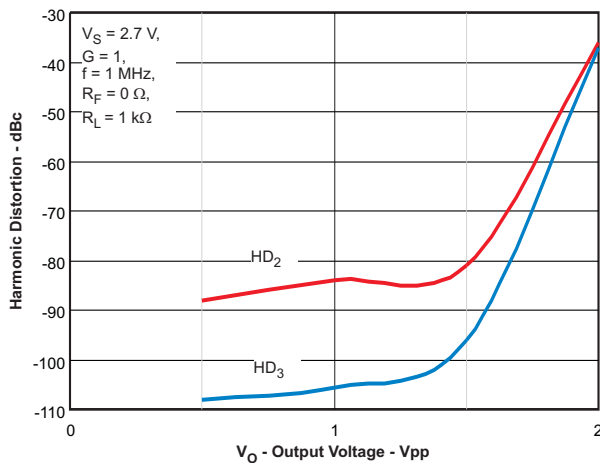


Figure 9. Harmonic Distortion vs Output Voltage

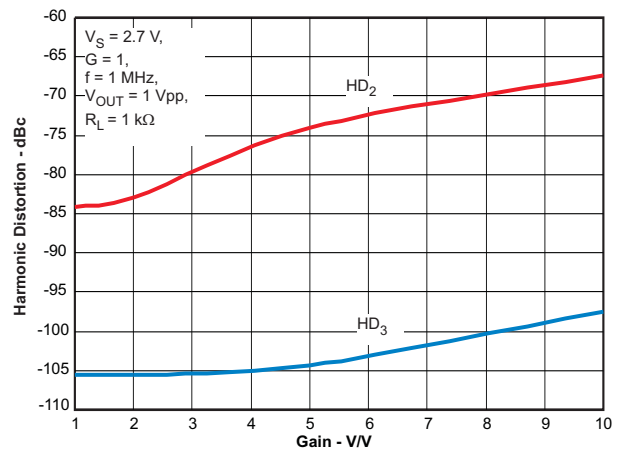


Figure 10. Harmonic Distortion vs Gain

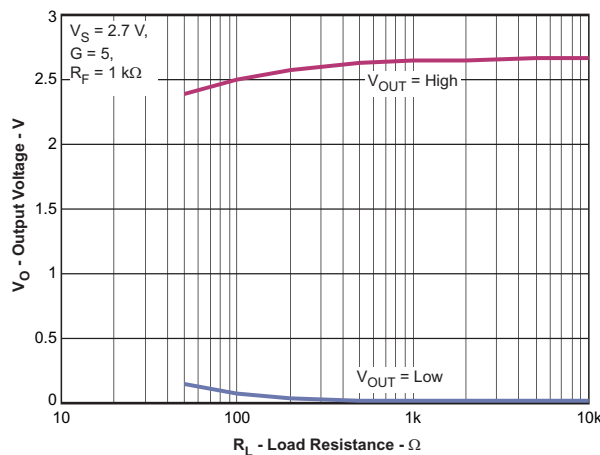


Figure 11. Output Voltage Swing vs Load Resistance

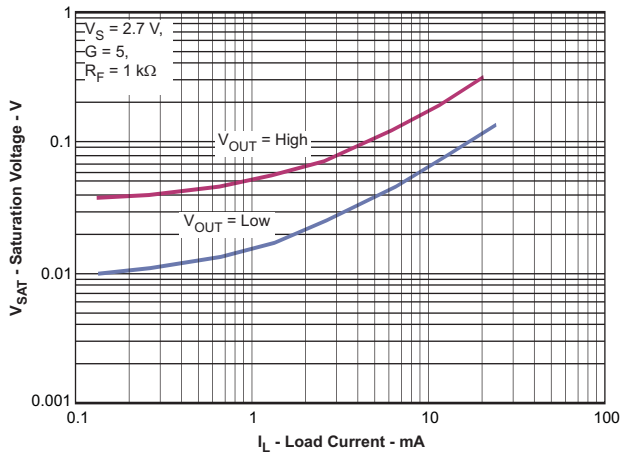


Figure 12. Output Saturation Voltage vs Load Current

TYPICAL PERFORMANCE GRAPHS: $V_S = 2.7\text{ V}$ (continued)

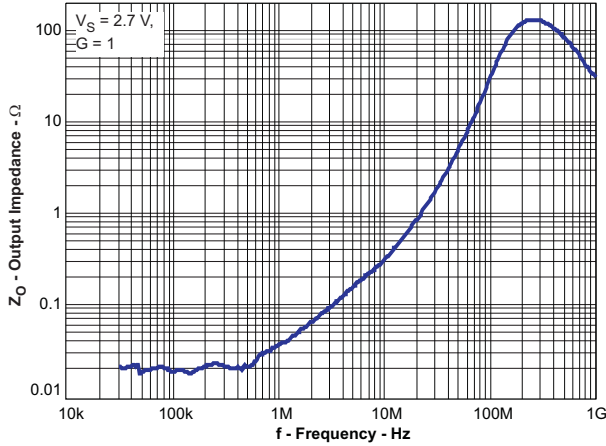


Figure 13. Output Impedance vs Frequency

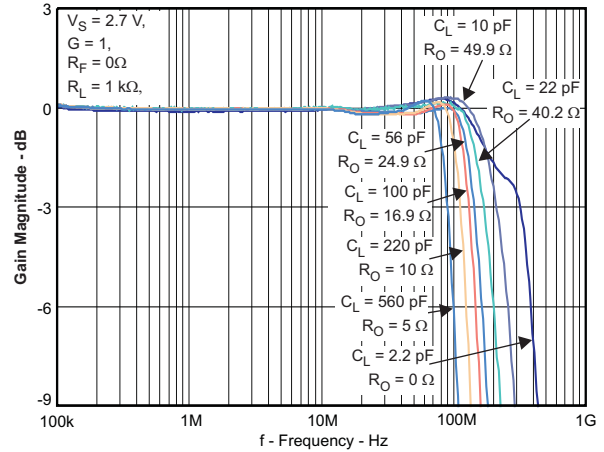


Figure 14. Frequency Response with Capacitive Load

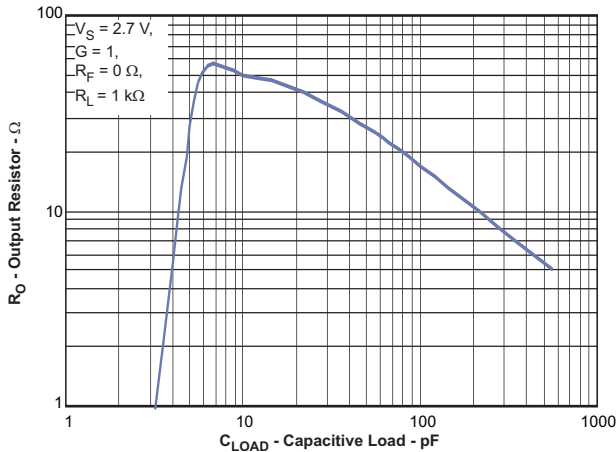


Figure 15. Series Output Resistor vs Capacitive Load

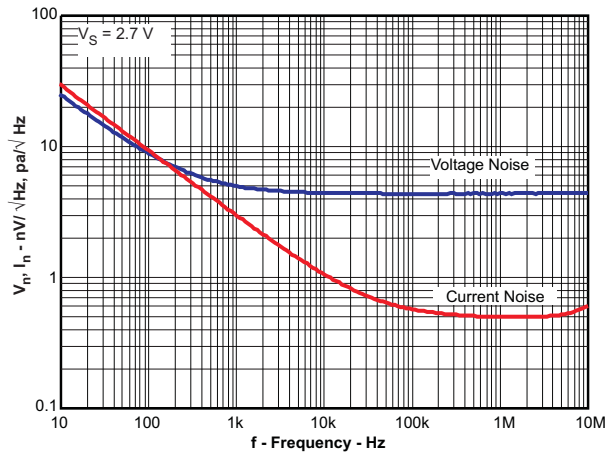


Figure 16. Input Referred Noise vs Frequency

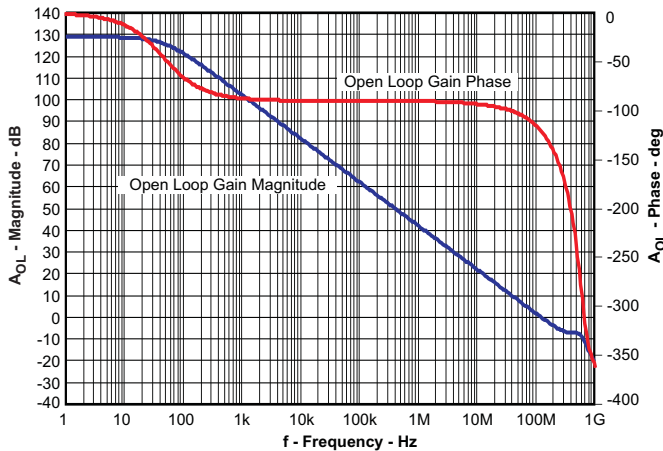


Figure 17. Open Loop Gain vs Frequency

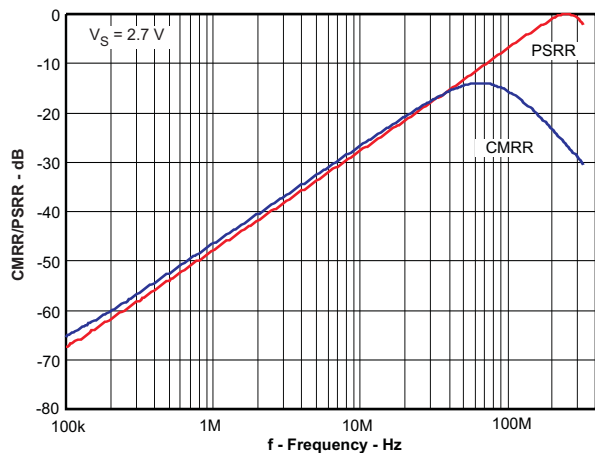


Figure 18. Common Mode/Power Supply Rejection Ratios vs Frequency

TYPICAL PERFORMANCE GRAPHS: $V_S = 2.7\text{ V}$ (continued)

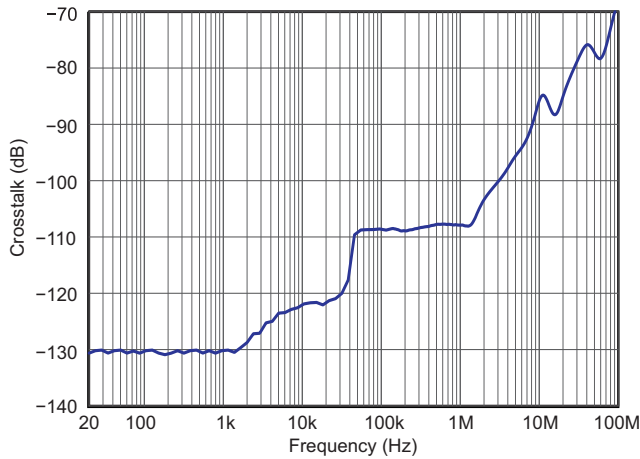


Figure 19. Crosstalk vs Frequency

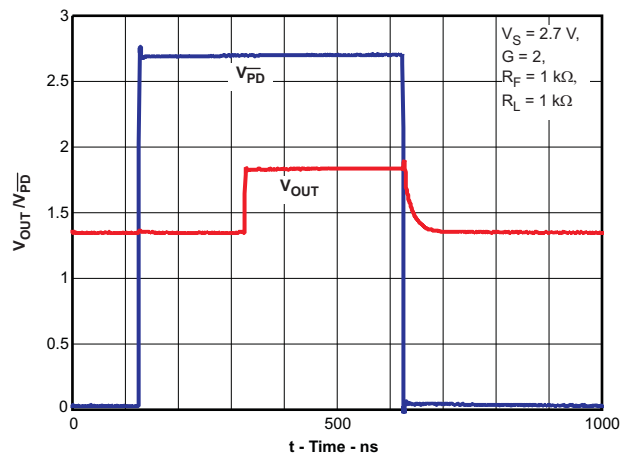


Figure 20. Power Down Response

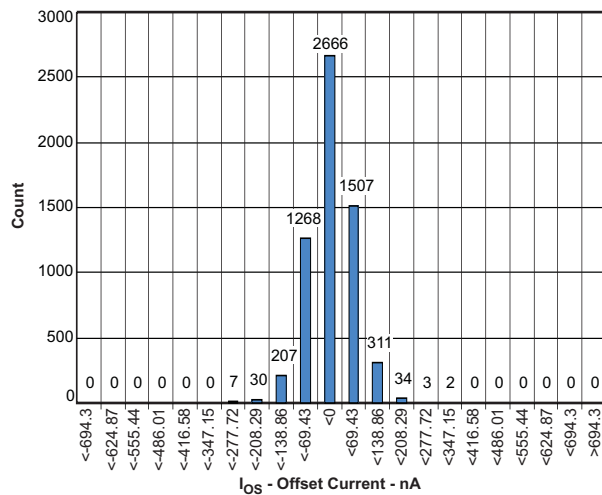


Figure 21. Input Offset Voltage

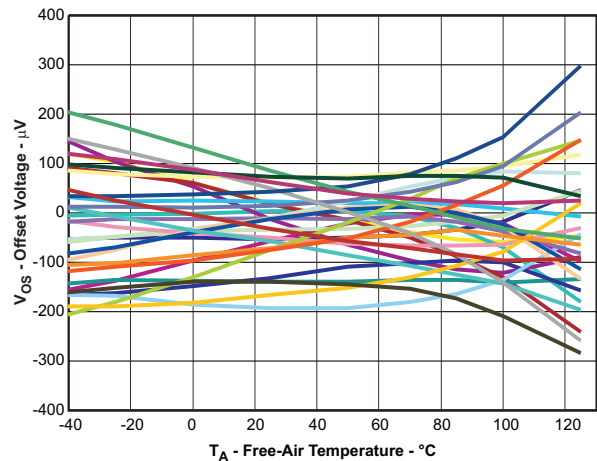


Figure 22. Input Offset Voltage vs Free-Air Temperature

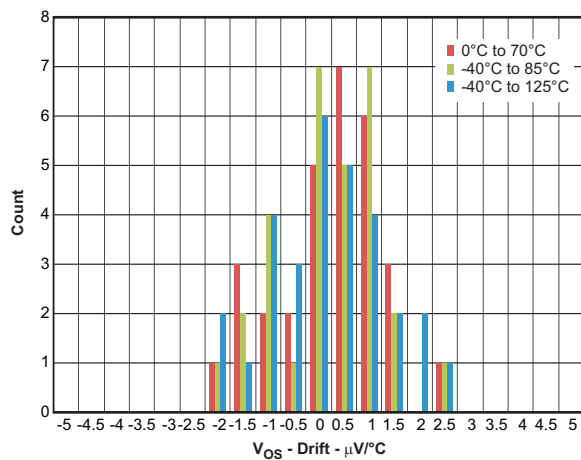


Figure 23. Input Offset Voltage Drift

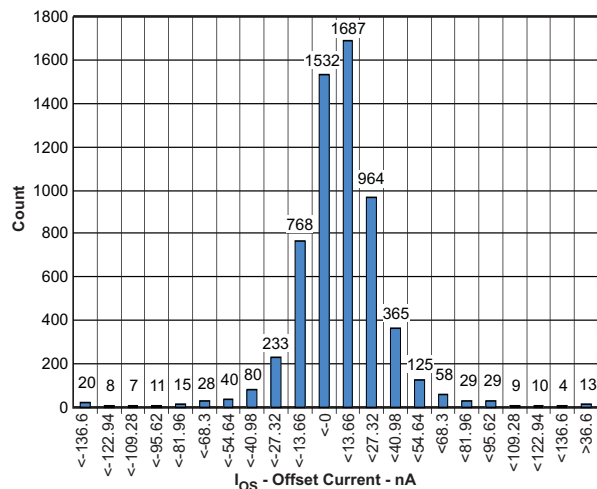


Figure 24. Input Offset Current

TYPICAL PERFORMANCE GRAPHS: $V_S = 2.7\text{ V}$ (continued)

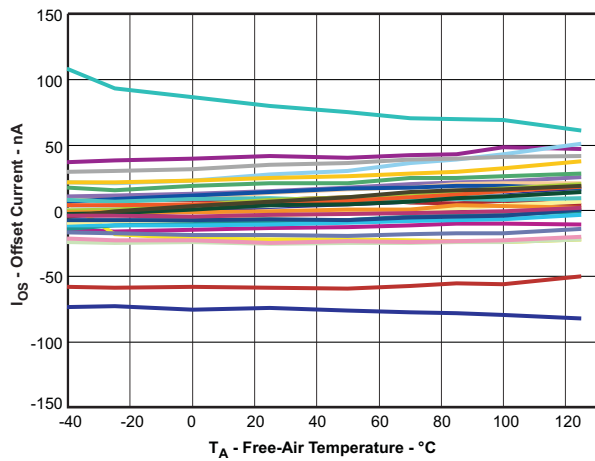


Figure 25. Input Offset Current vs Free-Air Temperature

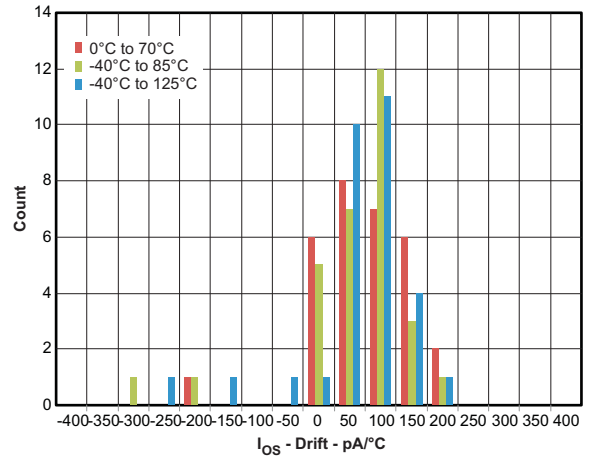


Figure 26. Input Offset Current Drift

TYPICAL PERFORMANCE GRAPHS: $V_S = 5\text{ V}$

Test conditions unless otherwise noted: $V_{S+} = +5\text{ V}$, $V_{S-} = 0\text{ V}$, $V_{OUT} = 2\text{ V}_{PP}$, $R_F = 0\ \Omega$, $R_L = 1\text{ k}\Omega$, $G = 1\text{ V/V}$, Input and Output Referenced to mid-supply unless otherwise noted. $T_A = 25^\circ\text{C}$.

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Input Offset Current	vs Free-Air Temperature	Figure 51
Input Offset Current Drift		Figure 52

TYPICAL PERFORMANCE GRAPHS: $V_S = 5\text{ V}$

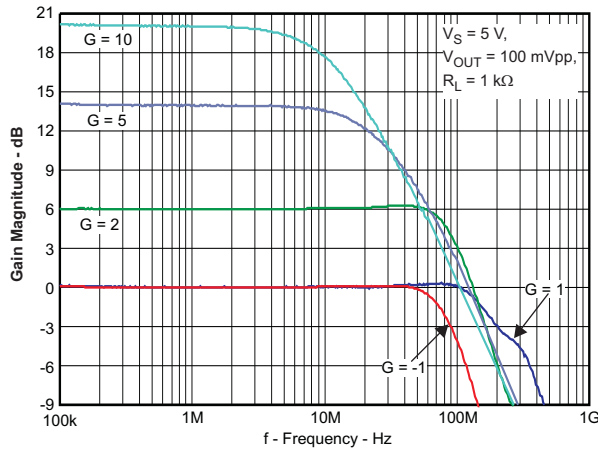


Figure 27. Small Signal Frequency Response

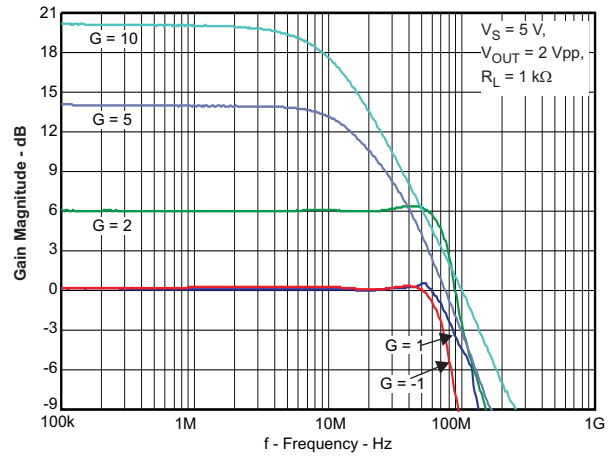


Figure 28. Large Signal Frequency Response

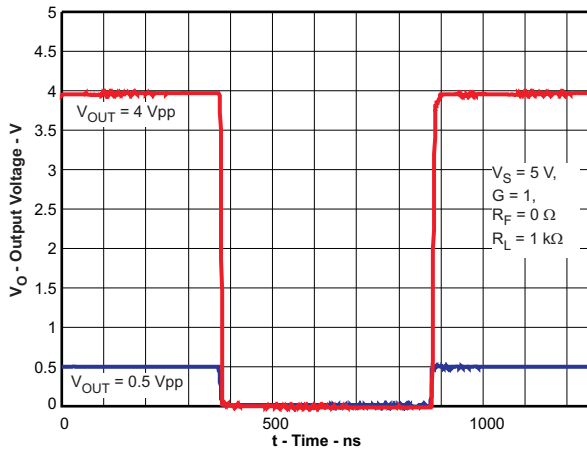


Figure 29. Noninverting Pulse Response

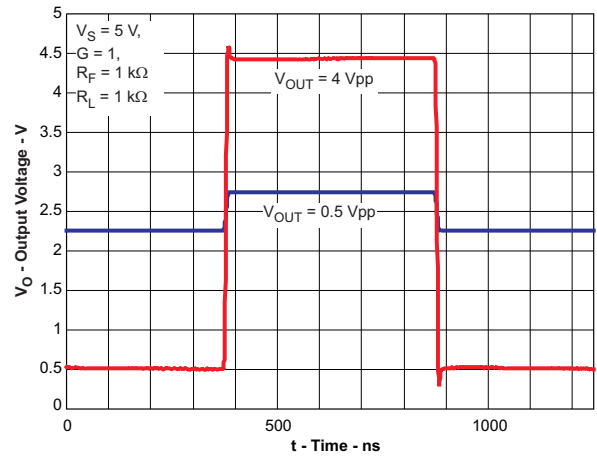


Figure 30. Inverting Pulse Response

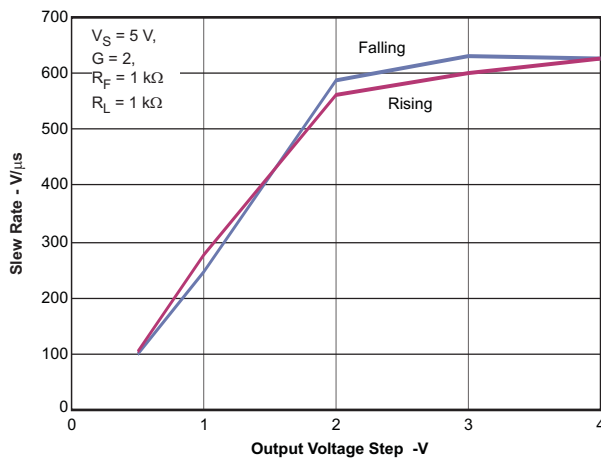


Figure 31. Slew Rate vs Output Voltage Step

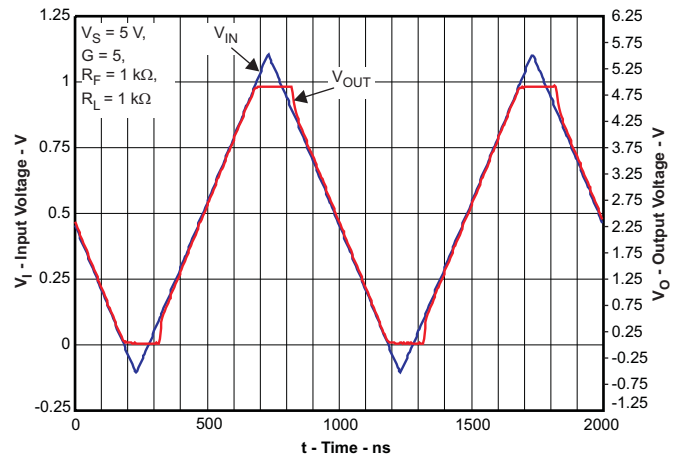


Figure 32. Output Overdrive Recovery

TYPICAL PERFORMANCE GRAPHS: $V_S = 5\text{ V}$ (continued)

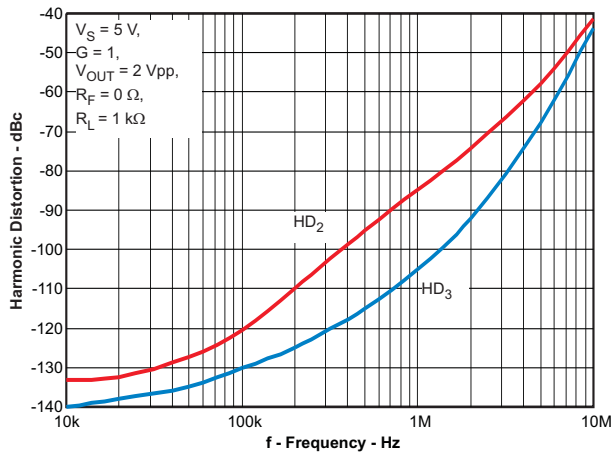


Figure 33. Harmonic Distortion vs Frequency

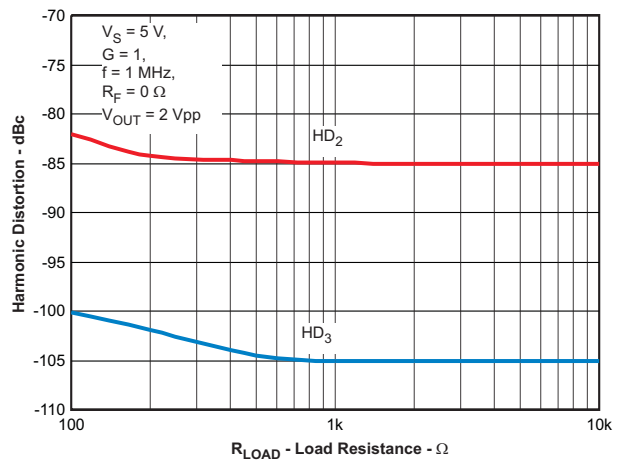


Figure 34. Harmonic Distortion vs Load Resistance

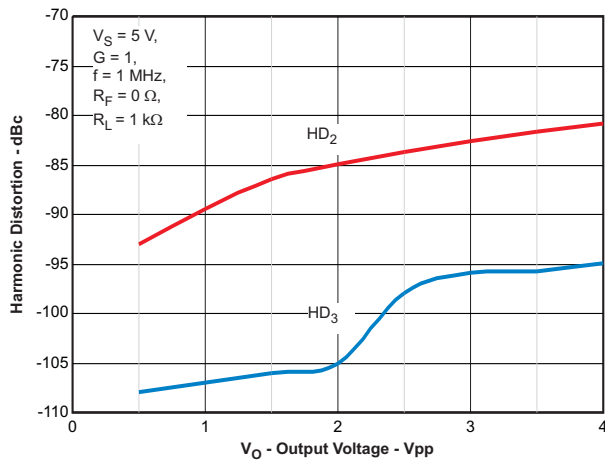


Figure 35. Harmonic Distortion vs Output Voltage

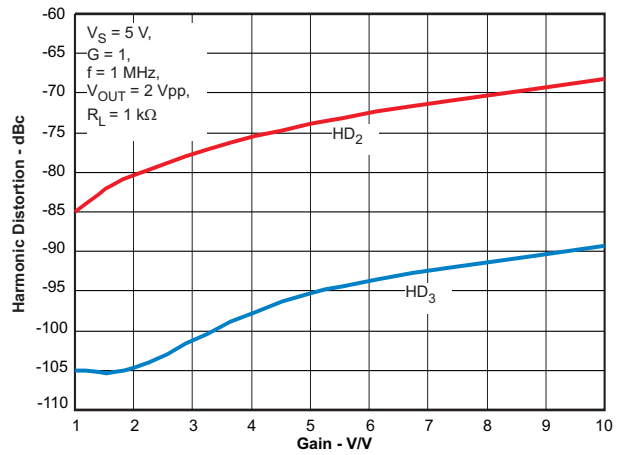


Figure 36. Harmonic Distortion vs Gain

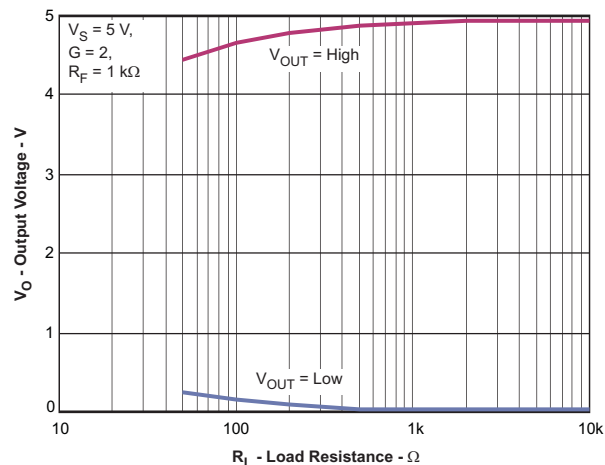


Figure 37. Output Voltage Swing vs Load Resistance

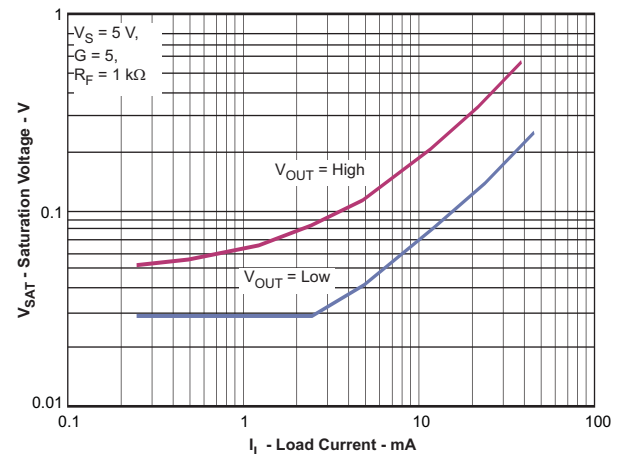


Figure 38. Output Saturation Voltage vs Load Current

TYPICAL PERFORMANCE GRAPHS: $V_S = 5\text{ V}$ (continued)

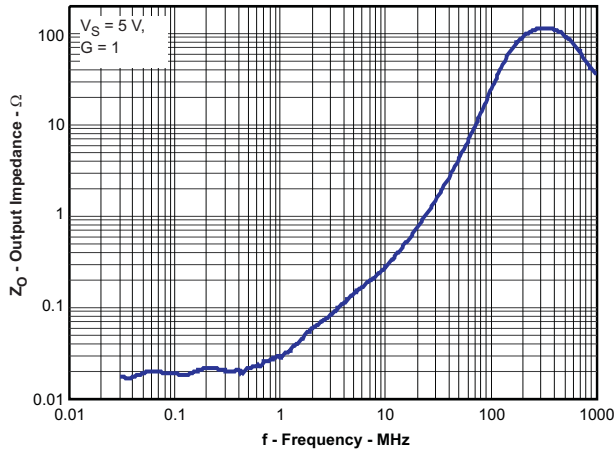


Figure 39. Output Impedance vs Frequency

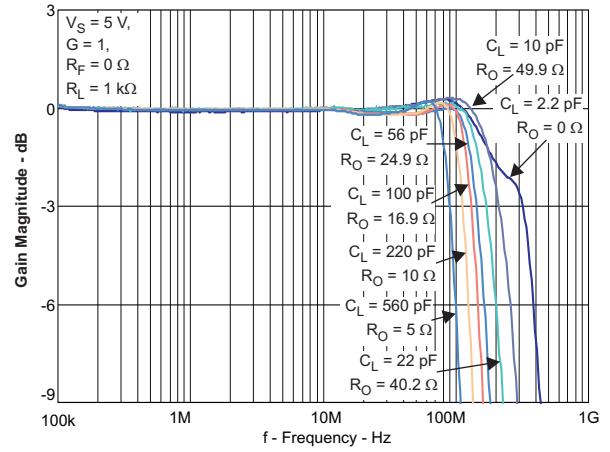


Figure 40. Frequency Response with Capacitive Load

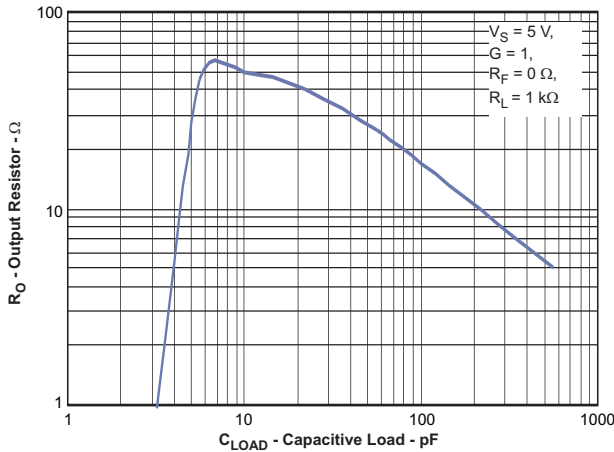


Figure 41. Series Output Resistor vs Capacitive Load

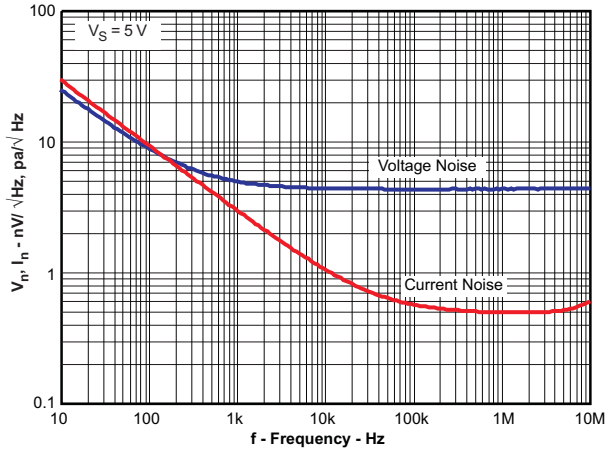


Figure 42. Input Referred Noise vs Frequency

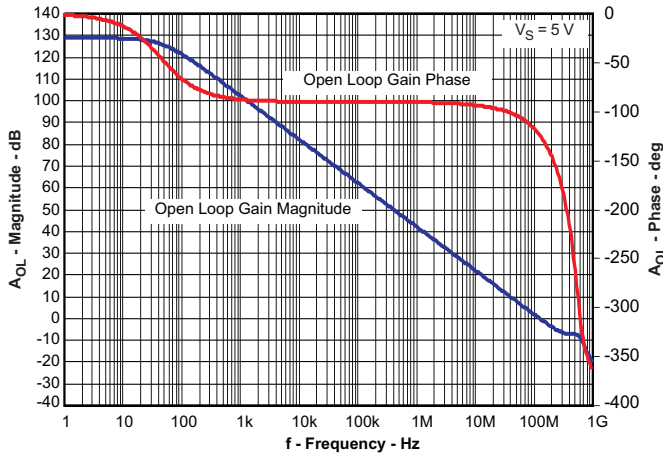


Figure 43. Open Loop Gain vs Frequency

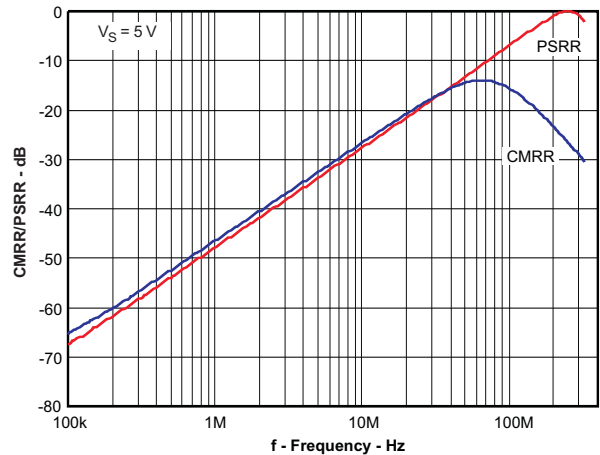


Figure 44. Common Mode/Power Supply Rejection Ratios vs Frequency

TYPICAL PERFORMANCE GRAPHS: $V_S = 5\text{ V}$ (continued)

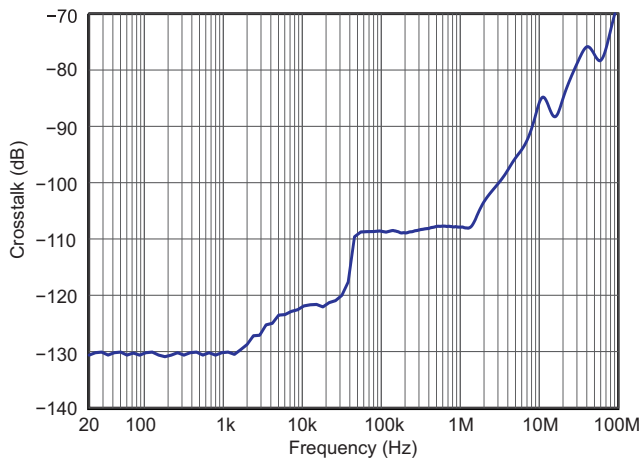


Figure 45. Crosstalk vs Frequency

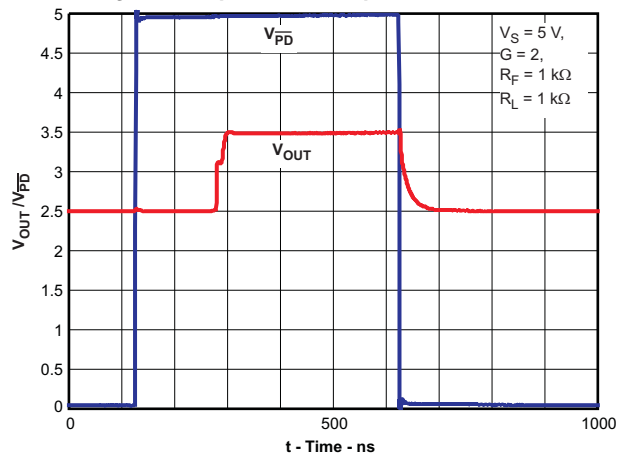


Figure 46. Power Down Response

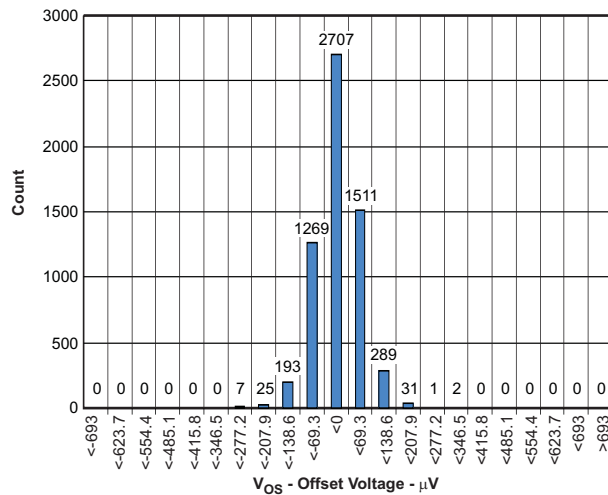


Figure 47. Input Offset Voltage

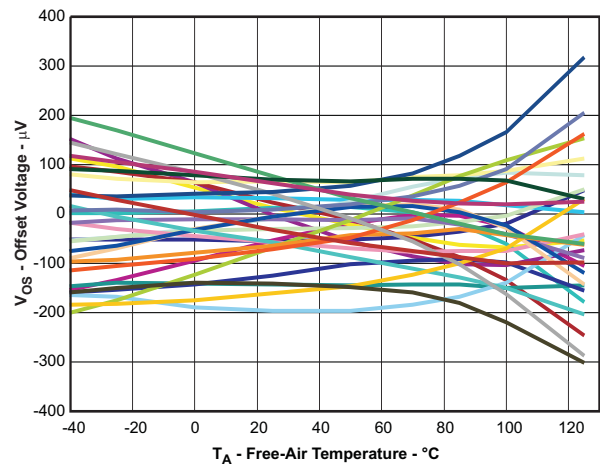


Figure 48. Input Offset Voltage vs Free-Air Temperature

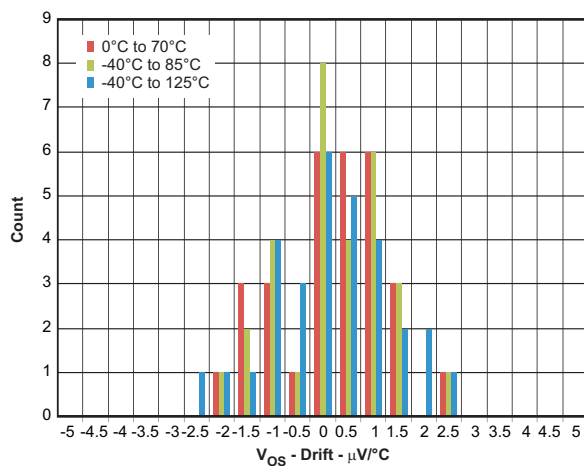


Figure 49. Input Offset Voltage Drift

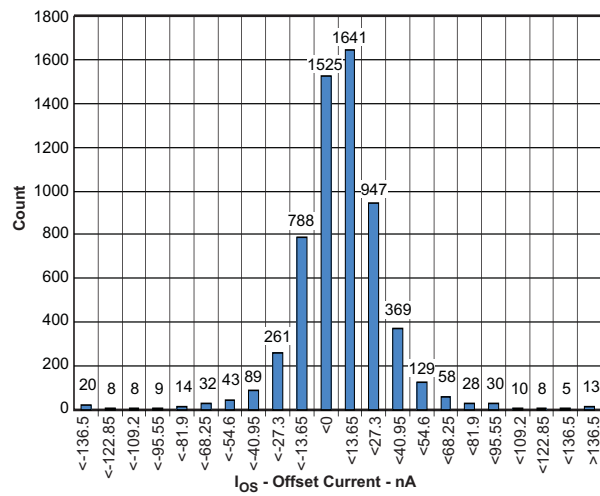


Figure 50. Input Offset Current

TYPICAL PERFORMANCE GRAPHS: $V_S = 5\text{ V}$ (continued)

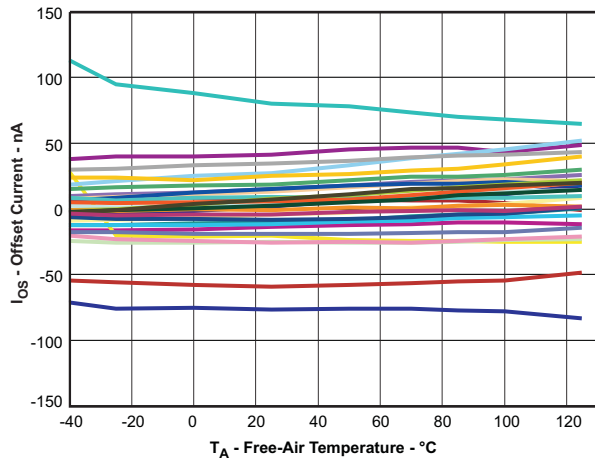


Figure 51. Input Offset Current vs Free-Air Temperature

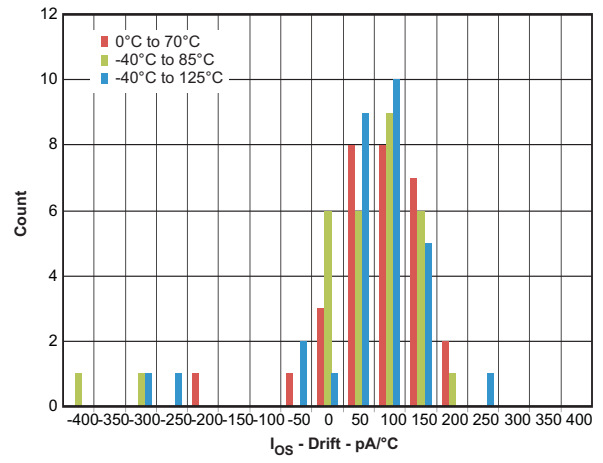


Figure 52. Input Offset Current Drift

APPLICATION INFORMATION

The following circuits show application information for the OPA836 and OPA2836. For simplicity, power supply decoupling capacitors are not shown in these diagrams.

Non-Inverting Amplifier

The OPA836 and OPA2836 can be used as non-inverting amplifiers with signal input to the non-inverting input, V_{IN+} . A basic block diagram of the circuit is shown in [Figure 53](#).

If we set $V_{IN} = V_{REF} + V_{SIG}$, then

$$V_{OUT} = V_{SIG} \left(1 + \frac{R_F}{R_G} \right) + V_{REF} \quad (1)$$

$$G = 1 + \frac{R_F}{R_G}$$

The signal gain of the circuit is set by: $G = 1 + \frac{R_F}{R_G}$, and V_{REF} provides a reference around which the input and output signals swing. Output signals are in-phase with the input signals.

The OPA836 and OPA2836 are designed for the nominal value of R_F to be $1k\Omega$ in gains other than +1. This gives excellent distortion performance, maximum bandwidth, best flatness, and best pulse response. $R_F = 1k\Omega$ should be used as a default unless other design goals require changing to other values. All test circuits used to collect data for this data sheet had $R_F = 1k\Omega$ for all gains other than +1. Gain of +1 is a special case where R_F is shorted and R_G is left open.

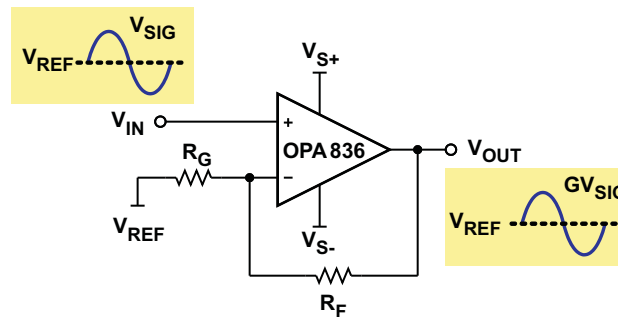


Figure 53. Non-Inverting Amplifier

Inverting Amplifier

The OPA836 and OPA2836 can be used as inverting amplifiers with signal input to the inverting input, V_{IN-} , through the gain setting resistor R_G . A basic block diagram of the circuit is shown in [Figure 54](#).

If we set $V_{IN} = V_{REF} + V_{SIG}$, then

$$V_{OUT} = V_{SIG} \left(\frac{-R_F}{R_G} \right) + V_{REF} \quad (2)$$

$$G = \frac{-R_F}{R_G}$$

The signal gain of the circuit is set by: $G = \frac{-R_F}{R_G}$ and V_{REF} provides a reference point around which the input and output signals swing. Output signals are 180° out-of-phase with the input signals. The nominal value of R_F should be $1k\Omega$ for inverting gains.

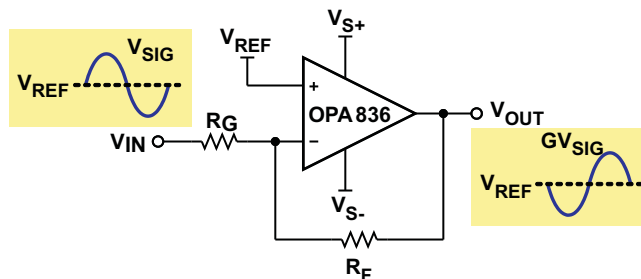


Figure 54. Inverting Amplifier

Attenuators

The non-inverting circuit of Figure 53 has minimum gain of 1. To implement attenuation, a resistor divider can be placed in series with the positive input, and the amplifier set for gain of 1 by shorting V_{OUT} to V_{IN-} and removing R_G . Since the op amp input is high impedance, the attenuation is set by the resistor divider.

The inverting circuit of Figure 54 can be used as an attenuator by making R_G larger than R_F . The attenuation is simply the resistor ratio. For example a 10:1 attenuator can be implemented with $R_F = 1\text{ k}\Omega$ and $R_G = 10\text{ k}\Omega$.

Single Ended to Differential Amplifier

Figure 55 shows an amplifier circuit that is used to convert single-ended signals to differential, and provides gain and level shifting. This circuit can be used for converting signals to differential in applications like line drivers for CAT 5 cabling or driving differential input SAR and $\Delta\Sigma$ ADCs.

By setting $V_{IN} = V_{REF} + V_{SIG}$, then

$$V_{OUT+} = G \times V_{IN} + V_{REF} \quad \text{and} \quad V_{OUT-} = -G \times V_{IN} + V_{REF} \quad \text{Where: } G = 1 + \frac{R_F}{R_G} \quad (3)$$

The differential signal gain of the circuit is $2x\ G$, and V_{REF} provides a reference around which the output signal swings. The differential output signal is in-phase with the single ended input signal.

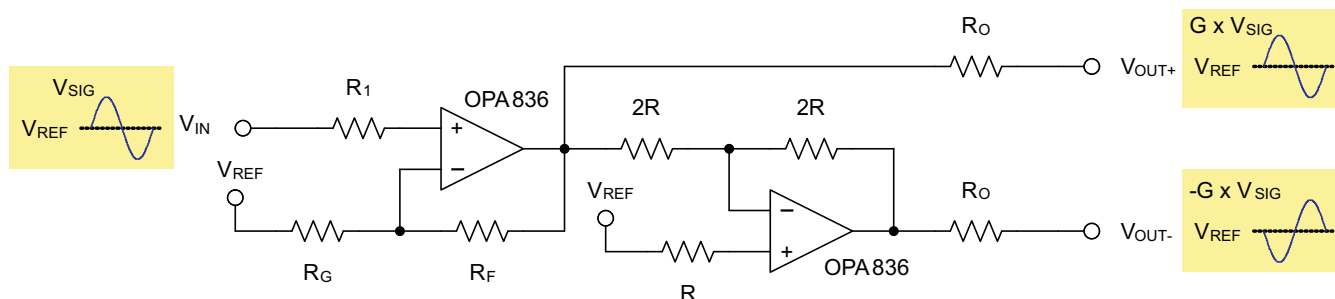


Figure 55. Single Ended to Differential Amplifier

Line termination on the output can be accomplished with resistors R_O . The impedance seen differential from the line will be $2x\ R_O$. For example if $100\ \Omega$ CAT 5 cable is used with double termination, the amplifier is typically set for a differential gain of 2 V/V (6 dB) with $R_F = 0\ \Omega$ (short) $R_G = \infty\ \Omega$ (open), $2R = 1\text{ k}\Omega$, $R1 = 0\ \Omega$, $R = 499\ \Omega$ to balance the input bias currents, and $R_O = 49.9\ \Omega$ for output line termination. This configuration is shown in Figure 56.

For driving a differential input ADC the situation is similar, but the output resistors, R_O , are typically chosen along with a capacitor across the ADC input for optimum filtering and settling time performance.

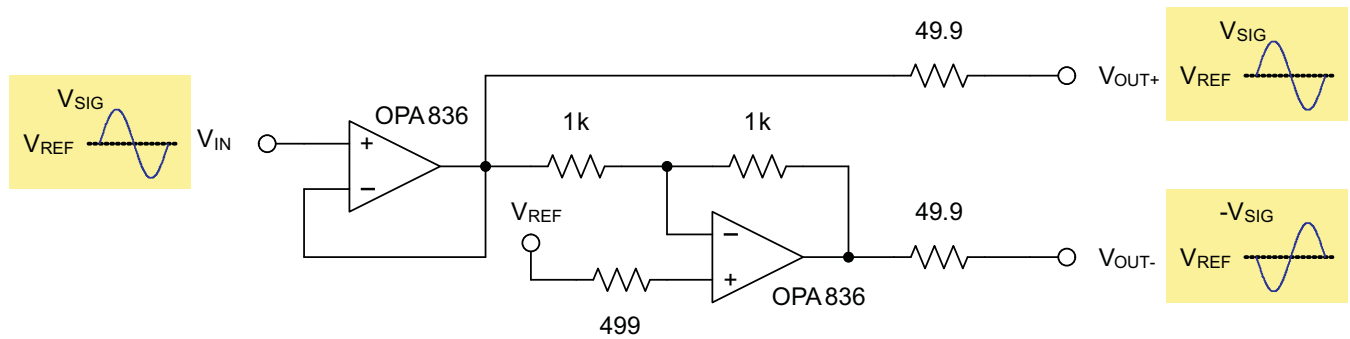


Figure 56. CAT 5 Line Driver with Gain = 2 V/V (6 dB)

Differential to Signal Ended Amplifier

Figure 57 shows a differential amplifier that is used to convert differential signals to single-ended and provides gain (or attenuation) and level shifting. This circuit can be used in applications like a line receiver for converting a differential signal from a CAT 5 cable to single-ended.

If we set $V_{IN+} = V_{CM} + V_{SIG+}$ and $V_{IN-} = V_{CM} + V_{SIG-}$, then

$$V_{OUT} = (V_{IN+} - V_{IN-}) \times \left(\frac{R_F}{R_G} \right) + V_{REF} \quad (4)$$

$$G = \frac{R_F}{R_G}$$

The signal gain of the circuit is set by: R_G , V_{CM} is rejected, and V_{REF} provides a level shift around which the output signal swings. The single ended output signal is in-phase with the differential input signal.

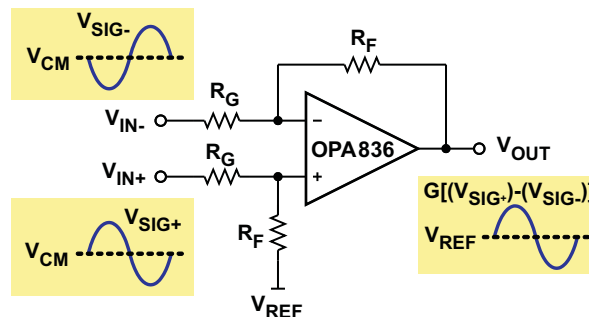


Figure 57. Differential to Single Ended Amplifier

Line termination can be accomplished with a resistor shunt across the input. The impedance seen differential from the line will be the resistor value in parallel with the amplifier circuit. For low gain and low line impedance the resistor value to add is approximately the impedance of the line. For example if 100 Ω CAT5 cable is used with a gain of 1 amplifier and $R_F = R_G = 1 \text{ k}\Omega$, adding a 100 Ω shunt across the input will give a differential impedance of 98 Ω; this should be adequate for most applications.

For best CMRR performance, resistors must be matched. A rule of thumb is $\text{CMRR} \approx$ the resistor tolerance; so 0.1% tolerance will provide about 60 dB CMRR.

Differential to Differential Amplifier

Figure 58 shows a differential amplifier that is used to amplify differential signals. This circuit has high input impedance and is often used in differential line driver applications where the signal source is a high impedance driver like a differential DAC that needs to drive a line.

If we set $V_{IN\pm} = V_{CM} + V_{SIG\pm}$ then

$$V_{OUT\pm} = V_{IN\pm} \times \left(1 + \frac{2R_F}{R_G}\right) + V_{CM} \tag{5}$$

$$G = 1 + \frac{2R_F}{R_G}$$

The signal gain of the circuit is set by: $G = 1 + \frac{2R_F}{R_G}$, and V_{CM} passes with unity gain. The amplifier in essence combines two non-inverting amplifiers into one differential amplifier with the R_G resistor shared, which makes R_G effectively $\frac{1}{2}$ its value when calculating the gain. The output signals are in-phase with the input signals.

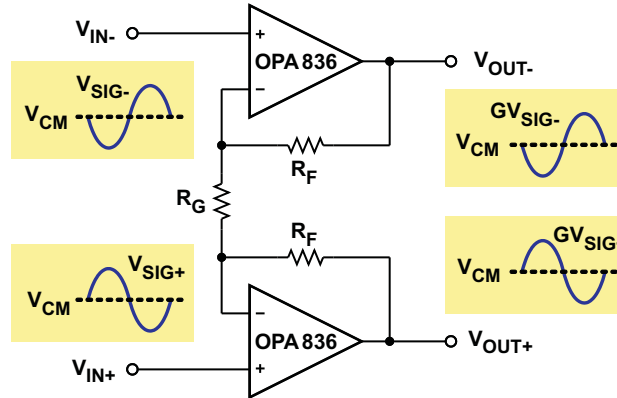


Figure 58. Differential to Differential Amplifier

Instrumentation Amplifier

Figure 59 is an instrumentation amplifier that combines the high input impedance of the differential to differential amplifier circuit and the common-mode rejection of the differential to single-ended amplifier circuit. This circuit is often used in applications where high input impedance is required like taps from a differential line or in cases where the signal source is a high impedance.

If we set $V_{IN+} = V_{CM} + V_{SIG+}$ and $V_{IN-} = V_{CM} + V_{SIG-}$, then

$$V_{OUT} = (V_{IN+} - V_{IN-}) \times \left(1 + \frac{2R_{F1}}{R_{G1}}\right) \left(\frac{R_{F2}}{R_{G2}}\right) + V_{REF} \tag{6}$$

The signal gain of the circuit is set by:

$G = \left(1 + \frac{2R_{F1}}{R_{G1}}\right) \left(\frac{R_{F2}}{R_{G2}}\right)$, V_{CM} is rejected, and V_{REF} provides a level shift around which the output signal swings. The single ended output signal is in-phase with the differential input signal.

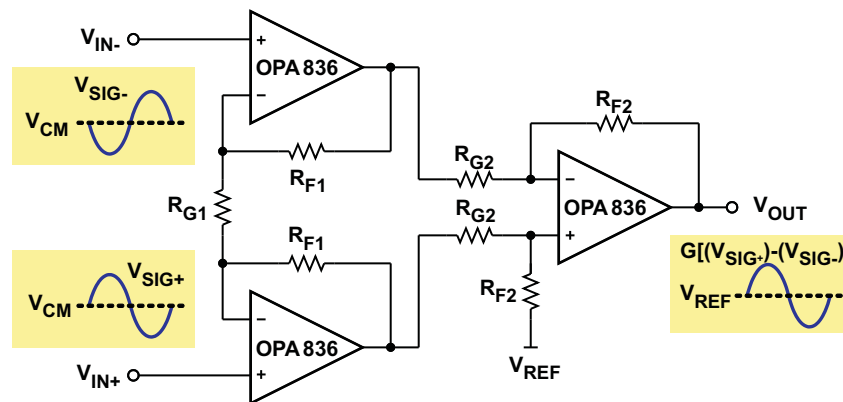


Figure 59. Instrumentation Amplifier

Integrated solutions are available, but the OPA836 provides a much lower power high frequency solution. For best CMRR performance, resistors must be matched. Assuming $CMRR \approx$ the resistor tolerance; so 0.1% tolerance will provide about 60 dB CMRR.

Gain Setting with OPA836 RUN Integrated Resistors

The OPA836 RUN package option includes integrated gain setting resistors for smallest possible footprint on a printed circuit board ($\approx 2\text{mm} \times 2\text{mm}$). By adding circuit traces on the PCB, gains of +1, -1, -1.33, +2, +2.33, -3, +4, -4, +5, -5.33, +6.33, -7, +8 and inverting attenuations of -0.1429, -0.1875, -0.25, -0.33, -0.75 can be achieved.

Figure 60 shows a simplified view of how the OPA836IRUN integrated gain setting network is implemented. Table 1 shows the required pin connections for various non-inverting and inverting gains (reference Figure 53 and Figure 54). Table 2 shows the required pin connections for various attenuations using the inverting amplifier architecture (reference Figure 54). Due to ESD protection devices being used on all pins, the absolute maximum and minimum input voltage range, $V_{S-} - 0.7\text{V}$ to $V_{S+} + 0.7\text{V}$, applies to the gain setting resistors, and so attenuation of large input voltages will require external resistors to implement.

The gain setting resistors are laser trimmed to 1% tolerance with nominal values of 1.6 k Ω , 1.2 k Ω , and 400 Ω . They have excellent temperature coefficient and gain tracking is superior to using external gain setting resistors. The 500 Ω and 1.5 pF capacitor in parallel with the 1.6 k Ω gain setting resistor provide compensation for best stability and pulse response.

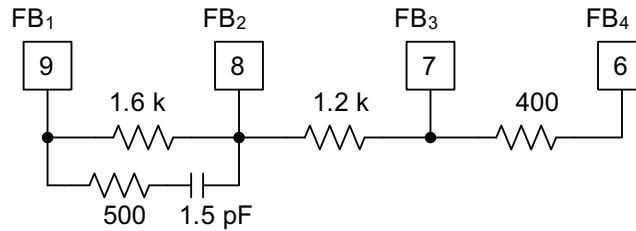


Figure 60. OPA836IRUN Gain Setting Network

Table 1. Gains Setting

Non-inverting Gain (Figure 53)	Inverting Gain (Figure 54)	Short Pins	Short Pins	Short Pins	Short Pins
1 V/V (0 dB)	-	1 to 9			-
2 V/V (6.02 dB)	-1 V/V (0 dB)	1 to 9	2 to 8	6 to GND	-
2.33 V/V (7.36 dB)	-1.33 V/V (2.5 dB)	1 to 9	2 to 8	7 to GND	-
4 V/V (12.04 dB)	-3 V/V (9.54 dB)	1 to 8	2 to 7	6 to GND	-
5 V/V (13.98 dB)	-4 V/V (12.04 dB)	1 to 9	2 to 7 or 8	7 to 8	6 to GND
6.33 V/V (16.03 dB)	-5.33 V/V (14.54 dB)	1 to 9	2 to 6 or 8	6 to 8	7 to GND
8 V/V (18.06 dB)	-7 V/V (16.90 dB)	1 to 9	2 to 7	6 to GND	-

Table 2. Attenuator Settings

Inverting Gain (Figure 54)	Short Pins	Short Pins	Short Pins	Short Pins
-0.75 V/V (-2.5 dB)	1 to 7	2 to 8	9 to GND	-
-0.333 V/V (-9.54 dB)	1 to 6	2 to 7	8 to GND	-
-0.25 V/V (-12.04 dB)	1 to 6	2 to 7 or 8	7 to 8	9 to GND
-0.1875 V/V (-14.54 dB)	1 to 7	2 to 6 or 8	6 to 8	9 to GND
-0.1429 V/V (-16.90 dB)	1 to 6	2 to 7	9 to GND	-

Input Common-Mode Voltage Range

When the primary design goal is a linear amplifier, with high CMRR, it is important to not violate the input common-mode voltage range (V_{ICR}) of an op amp.

Common-mode input range low and high specifications in the table data use CMRR to set the limit. The limits are chosen to ensure CMRR will not degrade more than 3dB below its limit if the input voltage is kept within the specified range. The limits cover all process variations and most parts will be better than specified. The typical specifications are from 0.2 V below the negative rail to 1.1 V below the positive rail.

Assuming the op amp is in linear operation the voltage difference between the input pins is very small (ideally 0 V) and input common-mode voltage can be analyzed at either input pin and the other input pin is assumed to be at the same potential. The voltage at V_{IN+} is easy to evaluate. In non-inverting configuration, [Figure 53](#), the input signal, V_{IN} , must not violate the V_{ICR} . In inverting configuration, [Figure 53](#), the reference voltage, V_{REF} , needs to be within the V_{ICR} .

The input voltage limits have fixed headroom to the power rails and track the power supply voltages. For with single 5 V supply, the linear input voltage range is -0.2 V to 3.9 V and with 2.7 V supply it is -0.2 V to 1.6V . The delta from each power supply rail is the same in either case; -0.2 V and 1.1 V.

Output Voltage Range

The OPA836 and OPA2836 are rail-to-rail output (RRO) op amps. Rail-to-rail output typically means the output voltage can swing to within a couple hundred milli-volts of the supply rails. There are different ways to specify this; one is with the output still in linear operation and another is with the output saturated. Saturated output voltages are closer to the power supply rails than linear outputs, but the signal is not a linear representation of the input. Linear output is a better representation of how well a device performs when used as a linear amplifier. Both saturation and linear operation limits are affected by the current in the output, where higher currents lead to more loss in the output transistors.

Data in the ELECTRICAL SPECIFICATIONS tables list both linear and saturated output voltage specifications with 1k Ω load. and show saturated voltage swing limits versus output load resistance and and show the output saturation voltage versus load current. Given a light load, the output voltage limits have nearly constant headroom to the power rails and track the power supply voltages. For example with 2 k Ω load and single 5 V supply the linear output voltage range is 0.15 V to 4.8 V and with 2.7 V supply it is 0.15 V to 2.5V. The delta from each power supply rail is the same in either case; 0.15 V and 0.2 V.

With devices like the OPA836 and OPA2836, where the input range is lower than the output range, it is typical that the input will limit the available signal swing only in non-inverting gain of 1. Signal swing in non-inverting configurations in gains $> +1$ and inverting configurations in any gain is generally limited by the output voltage limits of the op amp.

Split-Supply Operation (± 1.25 V to ± 2.75 V)

To facilitate testing with common lab equipment, the OPA836 EVM [SLOU314](#) is built to allow for split-supply operation. This configuration eases lab testing because the mid-point between the power rails is ground, and most signal generators, network analyzers, oscilloscopes, spectrum analyzers and other lab equipment reference their inputs and outputs to ground.

[Figure 61](#) shows a simple non-inverting configuration analogous to [Figure 53](#) with ± 2.5 V supply and V_{REF} equal to ground. The input and output will swing symmetrically around ground. Due to its ease of use, split supply operation is preferred in systems where signals swing around ground, but it requires generation of two supply rails.

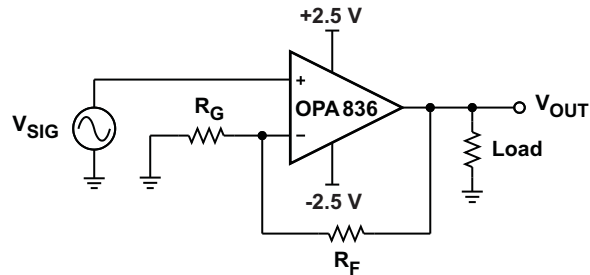


Figure 61. Split Supply Operation

Single-Supply Operation (2.5 V to 5.5 V)

Many newer systems use single power supply to improve efficiency and reduce the cost of the power supply. OPA836 and OPA2836 are designed for use with single-supply power operation and can be used with single-supply power with no change in performance from split supply as long as the input and output are biased within the linear operation of the device.

To change the circuit from split supply to single supply, level shift of all voltages by $\frac{1}{2}$ the difference between the power supply rails. For example, changing from ± 2.5 V split supply to 5 V single supply is shown conceptually in Figure 62.

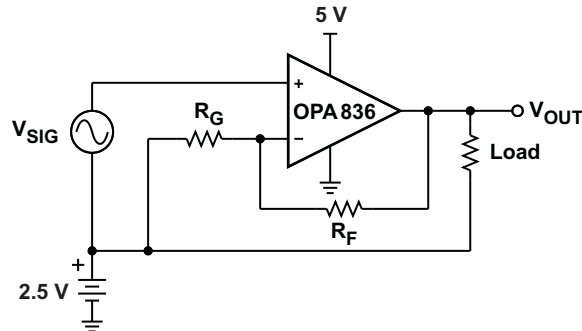


Figure 62. Single Supply Concept

A more practical circuit will have an amplifier or other circuit before to provide the bias voltage for the input and the output provides the bias for the next stage.

Figure 63 shows a typical non-inverting amplifier situation. With 5V single supply, a mid supply reference generator is needed to bias the negative side via R_G . To cancel the voltage offset that would otherwise be caused by the input bias currents, R_1 is chosen to be equal to R_F in parallel with R_G . For example if gain of 2 is required and $R_F = 1$ k Ω , select $R_G = 1$ k Ω to set the gain and $R_1 = 499$ Ω for bias current cancellation. The value for C is dependent on the reference, but at least 0.1 μ F is recommended to limit noise.

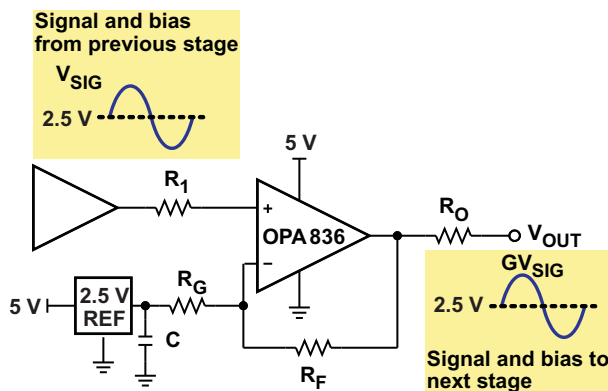


Figure 63. Non-Inverting Single Supply with Reference

Figure 64 shows a similar non-inverting single supply scenario with the reference generator replaced by the Thevenin equivalent using resistors and the positive supply. R_G' and R_G'' form a resistor divider from the 5 V supply and are used to bias the negative side with their parallel sum equal to the equivalent R_G to set the gain. To cancel the voltage offset that would otherwise be caused by the input bias currents, R_1 is chosen to be equal to R_F in parallel with R_G' in parallel with R_G'' ($R_1 = R_F || R_G' || R_G''$). For example if gain of 2 is required and $R_F = 1 \text{ k}\Omega$, selecting $R_G' = R_G'' = 2 \text{ k}\Omega$ gives equivalent parallel sum of $1 \text{ k}\Omega$, sets the gain to 2, and references the input to mid supply (2.5 V). R_1 is then set to 499Ω for bias current cancellation. This can be lower cost, but note the extra current draw required in the resistor divider.

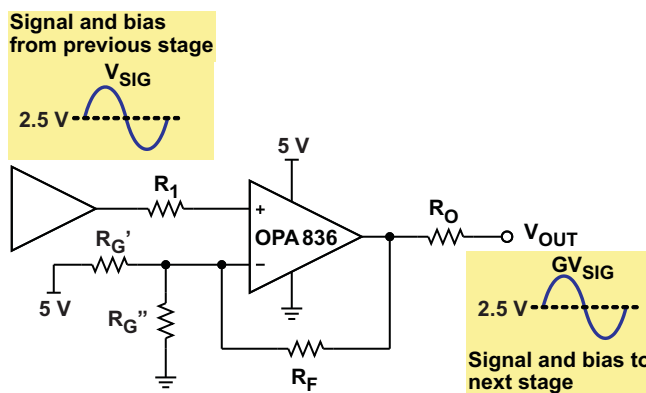


Figure 64. Non-Inverting Single Supply with Resistors

Figure 65 shows a typical inverting amplifier situation. With 5V single supply, a mid supply reference generator is needed to bias the positive side via R_1 . To cancel the voltage offset that would otherwise be caused by the input bias currents, R_1 is chosen to be equal to R_F in parallel with R_G . For example if gain of -2 is required and $R_F = 1 \text{ k}\Omega$, select $R_G = 499 \Omega$ to set the gain and $R_1 = 332 \Omega$ for bias current cancellation. The value for C is dependent on the reference, but at least $0.1 \mu\text{F}$ is recommended to limit noise into the op amp.

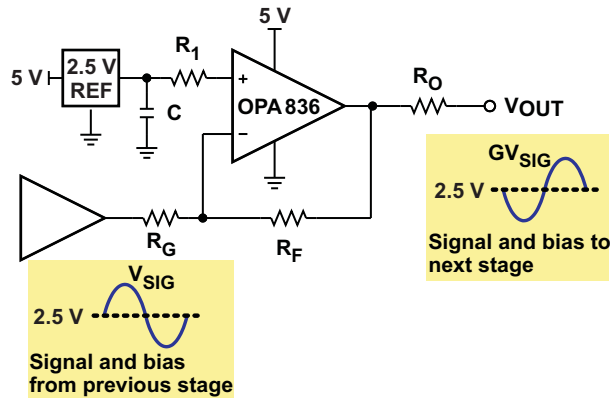


Figure 65. Inverting Single Supply with Reference

Figure 66 shows a similar inverting single supply scenario with the reference generator replaced by the Thevenin equivalent using resistors and the positive supply. R_1 and R_2 form a resistor divider from the 5 V supply and are used to bias the positive side. To cancel the voltage offset that would otherwise be caused by the input bias currents, set the parallel sum of R_1 and R_2 equal to the parallel sum of R_F and R_G . C should be added to limit coupling of noise into the positive input. For example if gain of -2 is required and $R_F = 1\text{ k}\Omega$, select $R_G = 499\ \Omega$ to set the gain. $R_1 = R_2 = 665\ \Omega$ for mid supply voltage bias and for op amp input bias current cancellation. A good value for C is $0.1\ \mu\text{F}$. This can be lower cost, but note the extra current draw required in the resistor divider.

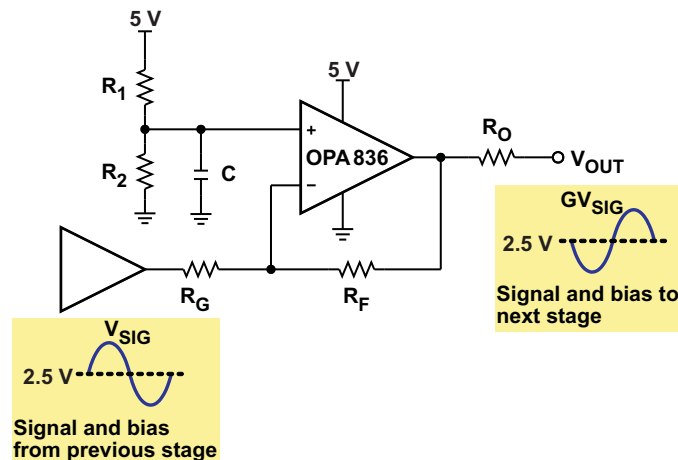


Figure 66. Inverting Single Supply with Resistors

Pulse Application with Single-Supply

For pulsed applications, where the signal is at ground and pulses to some positive or negative voltage, the circuit bias voltage considerations are different than with a signal that swings symmetrical about a reference point and the circuit configuration should be adjusted accordingly. Figure 67 shows a pulsed situation where the signal is at ground (0 V) and pulses to a positive value.

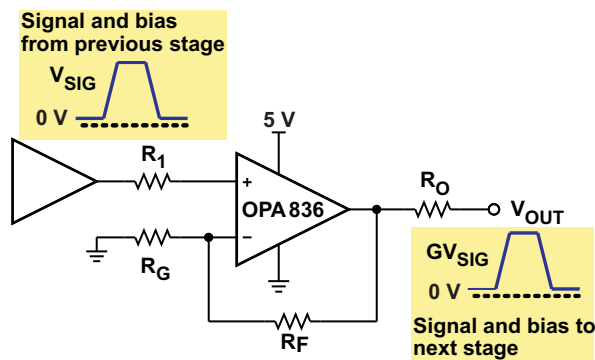


Figure 67. Non-Inverting Single Supply with Pulse

If the input signal pulses negative from ground, an inverting amplifier is more appropriate as shown in Figure 68. A key consideration in both non-inverting and inverting cases is that the input and output voltages are kept within the limits of the amplifier, and since the V_{ICR} of the OPA836 includes the negative supply rail, the op amp lends itself to this application.

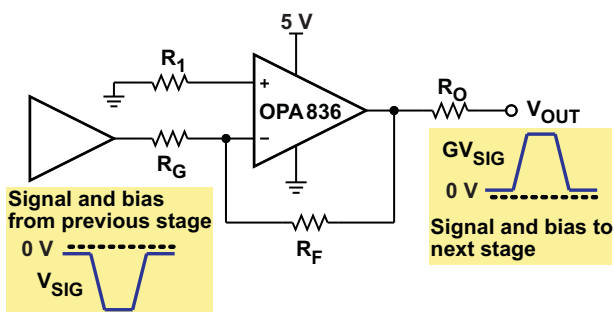


Figure 68. Inverting Single Supply with Pulse

Power-Down Operation

The OPA836 and OPA2836 include a power-down mode. Under logic control, the amplifiers can be switched from normal operation to a standby current of $<1.5\mu\text{A}$. When the $\overline{\text{PD}}$ pin is connected high, the amplifier is active. Connecting $\overline{\text{PD}}$ pin low disables the amplifier, and places the output in a high impedance state. Note: the op amp's output in gain of +1 is high impedance similar to a 3-state high impedance gate, but in other gains the feedback network is a parallel load.

The $\overline{\text{PD}}$ pin must be actively driven high or low and should not be left floating. If the power-down mode is not used, $\overline{\text{PD}}$ should be tied to the positive supply rail.

$\overline{\text{PD}}$ logic states are TTL with reference to the negative supply rail, V_{S-} . When the op amp is powered from single supply and ground, driving from logic devices with similar V_{DD} voltages to the op amp should not require any special consideration. When the op amp is powered from split supply, V_{S-} is below ground and an open collector type of interface with pull-up resistor is more appropriate. Pull-up resistor values should be lower than 100k and the drive logic should be negated due to the inverting action of an open collector gate.

Low Power Applications and the Effects of Resistor Values on Bandwidth

The OPA836 and OPA2836 are designed for the nominal value of R_F to be 1 k Ω in gains other than +1. This gives excellent distortion performance, maximum bandwidth, best flatness, and best pulse response. It also loads the amplifier. For example; in gain of 2 with $R_F = R_G = 1$ k Ω , R_G to ground, and $V_{OUT} = 4$ V, 2 mA of current will flow through the feedback path to ground. In gain of +1, R_G is open and no current will flow to ground. In low power applications, it is desirable to reduce this current by increasing the gain setting resistors values. Using larger value gain resistors has two primary side effects (other than lower power) due to their interaction with parasitic circuit capacitance.

1. Lowers the bandwidth.
2. Lowers the phase margin
 - (a) This will cause peaking in the frequency response.
 - (b) And will cause over shoot and ringing in the pulse response.

Figure 69 shows the small signal frequency response on OPA836EVM for non-inverting gain of 2 with R_F and R_G equal to 1 k Ω , 10 k Ω , and 100k Ω . The test was done with $R_L = 1$ k Ω . Due to loading effects of R_L , lower values may reduce the peaking, but higher values will not have a significant effect.

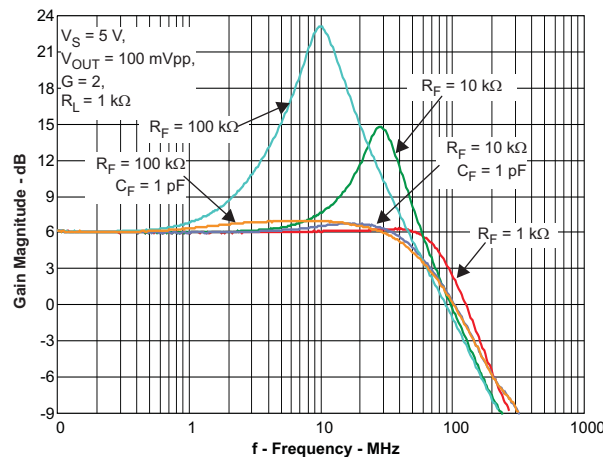


Figure 69. Frequency Response with Various Gain Setting Resistor Values

As expected, larger value gain resistors cause lower bandwidth and peaking in the response (peaking in frequency response is synonymous with overshoot and ringing in pulse response). Adding 1 pF capacitors in parallel with R_F helps compensate the phase margin and restores flat frequency response. Figure 70 shows the test circuit used.

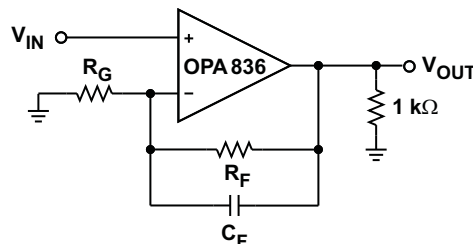


Figure 70. G = 2 Test Circuit for Various Gain Setting Resistor Values

Driving Capacitive Loads

The OPA836 and OPA2836 can drive up to a nominal capacitive load of 2.2 pF on the output with no special consideration. When driving capacitive loads greater than this, it is recommended to use a small resistor (R_O) in series with the output as close to the device as possible. Without R_O , capacitance on the output will interact with the output impedance of the amplifier causing phase shift in the loop gain of the amplifier that will reduce the phase margin. This will cause peaking in the frequency response and overshoot and ringing in the pulses response. Interaction with other parasitic elements may lead to instability or oscillation. Inserting R_O will isolate the phase shift from the loop gain path and restore the phase margin; however, it will also limit the bandwidth.

Figure 71 shows the test circuit and shows the recommended values of R_O versus capacitive loads, C_L . See for frequency response with various values.

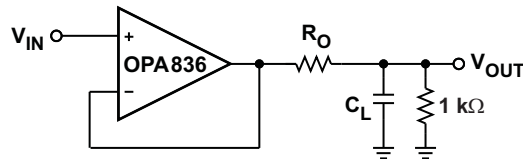


Figure 71. R_O versus C_L Test Circuit

Active Filters

The OPA836 and OPA2836 can be used to design active filters. Figure 73 and Figure 72 show MFB and Sallen-Key circuits designed using FilterPro™ <http://focus.ti.com/docs/toolsw/folders/print/filterpro.html> to implement 2nd order low-pass butterworth filter circuits. Figure 74 shows the frequency response.

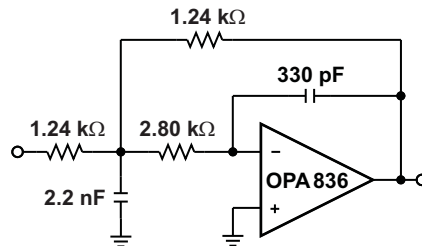


Figure 72. MFB 100kHz 2nd Order Low-Pass Butterworth Filter Circuit

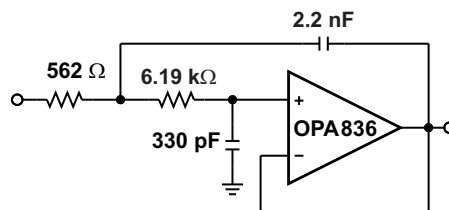


Figure 73. Sallen-Key 100kHz 2nd Order Low-Pass Butterworth Filter Circuit

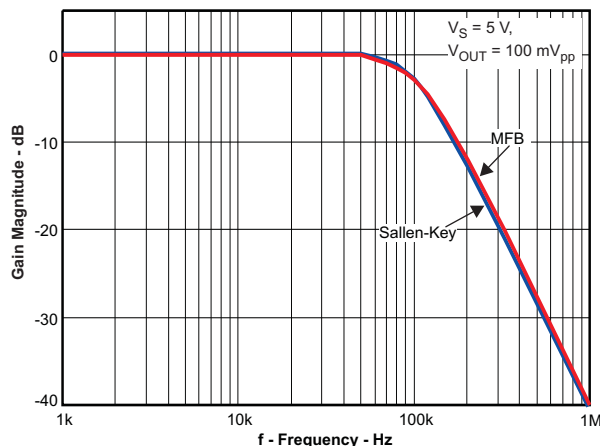


Figure 74. MFB and Sallen-Key 2nd Order Low-Pass Butterworth Filter Response

MFB and Sallen-Key filter circuits offer similar performance. The main difference is the MFB is an inverting amplifier in the pass band and the Sallen-Key is non-inverting. The primary pro for each is the Sallen-Key in unity gain has no resistor gain error term, and thus no sensitivity to gain error, while the MFB has inherently better attenuation properties beyond the bandwidth of the op amp.

Audio Frequency Performance

The OPA836 and OPA2836 provide excellent audio performance with very low quiescent power. To show performance in the audio band, a 2700 series Audio Analyzer from Audio Precision was used to test THD+N and FFT at 1V_{RMS} output voltage. Figure 75 is the test circuit used. Note the 100pF capacitor to ground on the input helped to decouple noise pick up in the lab and improved noise performance.

Figure 76 shows the THD+N performance with 100kΩ and 300Ω loads, with A-weighting, and with no weighting. Both loads show similar performance. With no weighting the THD+N performance is dominated by the noise whereas A-weighting provides filtering that improves the noise.

Figure 77 and Figure 78 show FFT output with a 1 kHz tone and 100kΩ and 300Ω loads. To show relative performance of the device versus the test set, one channel has the OPA836 in line between generator output and analyzer input and the other channel is in “Gen Mon” loopback mode, which internally connects the signal generator to the analyzer input. With 100 kΩ load, Figure 77, the curves are basically indistinguishable from each other except for noise, which means the OPA836 cannot be directly measured. With 300 Ω load, Figure 78, the main difference between the curves is OPA836 shows slightly higher even order harmonics, but odd order is masked by the test set performance.

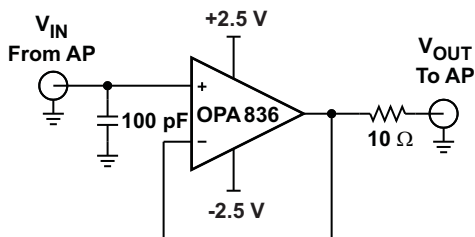


Figure 75. OPA836 AP Analyzer Test Circuit

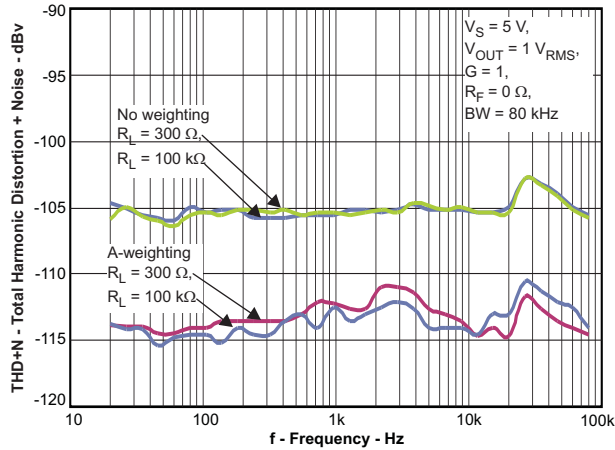


Figure 76. OPA836 1Vrms 20 Hz to 80 kHz THD+N

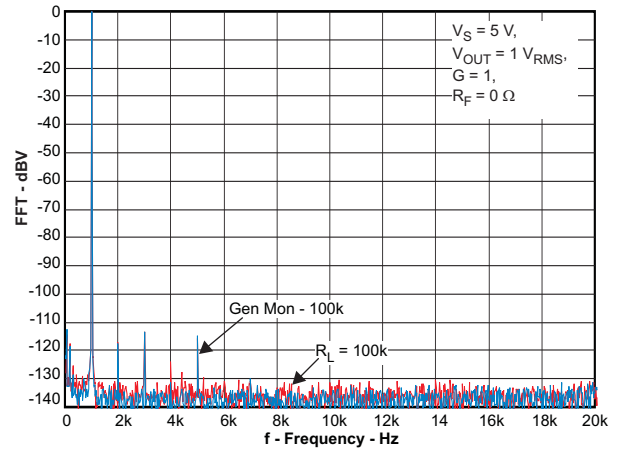


Figure 77. OPA836 and AP Gen Mon 10kHz FFT Plot; $V_{OUT} = 1 V_{RMS}$, $R_L = 100 k\Omega$

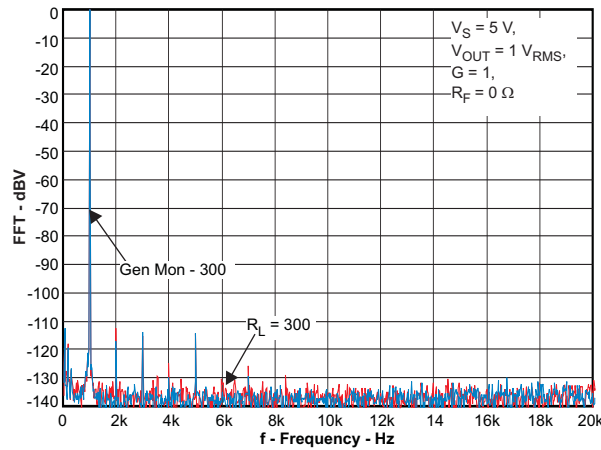


Figure 78. OPA836 and AP Gen Mon 10 kHz FFT Plot; $V_{OUT} = 1 V_{RMS}$, $R_L = 300\Omega$

ADC Driver Performance

The OPA836 provides excellent performance when driving high performance delta-sigma ($\Delta\Sigma$) and successive approximation register (SAR) ADCs in low power audio and industrial applications.

OPA836 and ADS8326 Combined Performance

To show achievable performance, the OPA836 is tested as the drive amplifier for the ADS8326. The ADS8326 is a 16-bit, micro power, SAR ADC with pseudo-differential inputs and sample rates up to 250 kSPS. It offers excellent noise and distortion performance in a small 8-pin SOIC or VSSOP (MSOP) package. Low power and small size make the ADS8326 and OPA836 an ideal solution for portable and battery-operated systems, for remote data-acquisition modules, simultaneous multichannel systems, and isolated data acquisition.

The circuit shown in Figure 79 is used to test the performance, Figure 80 is the FFT plot with 10 kHz input frequency showing the spectral performance, and the tabulated AC analysis results are in Table 3.

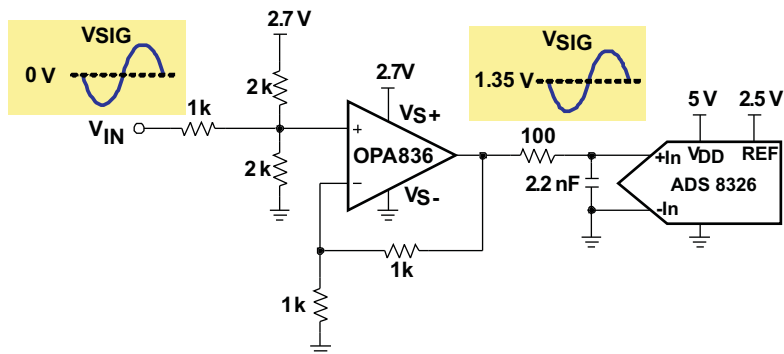


Figure 79. OPA836 and ADS8326 Test Circuit

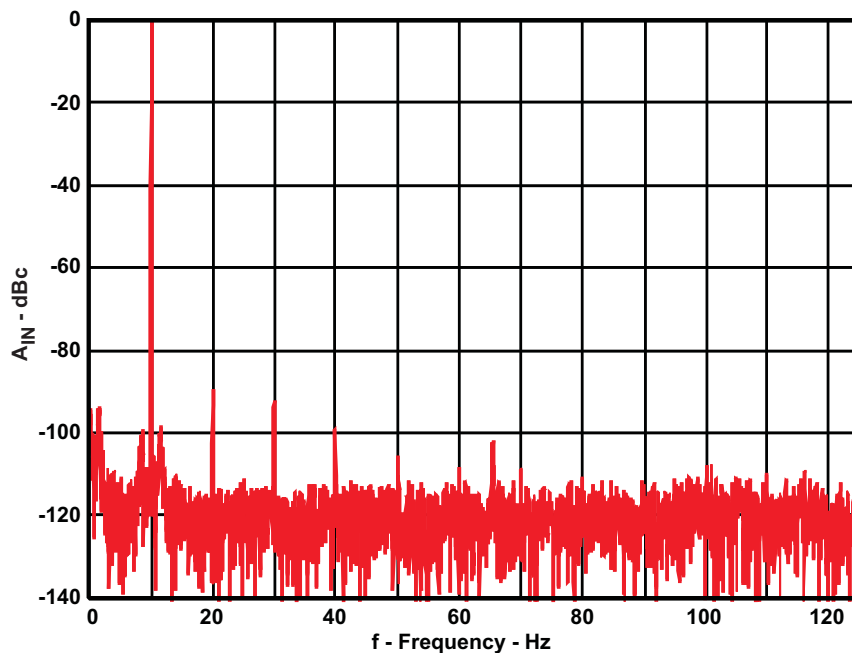


Figure 80. ADS8326 and OPA836 10kHz FFT

Table 3. AC Analysis

Tone (Hz)	Signal (dBFS)	SNR (dBc)	THD (dBc)	SINAD (dBc)	SFDR (dBc)
10k	-0.85	83.3	-86.6	81.65	88.9

Layout Recommendations

The OPA836 EVM (SLOU314) should be used as a reference when designing the circuit board. It is recommended to follow the EVM layout of the external components near to the amplifier, ground plane construction, and power routing as closely as possible. General guidelines are:

1. Signal routing should be direct and as short as possible into an out of the op amp.
2. The feedback path should be short and direct avoiding vias if possible especially with $G = +1$.
3. Ground or power planes should be removed from directly under the amplifier's negative input and output pins.
4. A series output resistor is recommended to be placed as near to the output pin as possible. See "Recommended Series Output Resistor vs. Capacitive Load" () for recommended values given expected capacitive load of design.
5. A 2.2 μF power supply decoupling capacitor should be placed within 2 inches of the device and can be shared with other op amps. For spit supply, a capacitor is required for both supplies.
6. A 0.1 μF power supply decoupling capacitor should be placed as near to the power supply pins as possible. Preferably within 0.1 inch. For split supply, a capacitor is required for both supplies.
7. The $\overline{\text{PD}}$ pin uses TTL logic levels. If not used it should tied to the positive supply to enable the amplifier. If used, it must be actively driven. A bypass capacitor is not necessary, but can be used for robustness in noisy environments.

REVISION HISTORY

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision D (October 2011) to Revision E	Page
• Added OPA2836 RMC 封装至本文档	1
• Added RMC 封装至 描述部分	1
• Deleted Packaging/Ordering Information table, leaving only note to POA	2
• Added OPA2836 RMC package to Thermal Information table	2
• Added OPA2839 RMC designator to OPA2836 RUN pin out diagram	9
• Added OPA2836 RMC pin definitions to Pin Functions table	11

Changes from Revision A (March 2011) to Revision B	Page
• Changed 将 OPA836 从产品预览改为生产数据	1

Changes from Revision B (May 2011) to Revision C	Page
• 已将“OPA836 RUN 封装...” 文本添加到描述中	1
• Removed Product Preview from all devices except OPA836IRUNT and OPA836IRUNR	2
• Replaced the TBD values in the Thermal Information table	2
• Changed - Channel to channel crosstalk (OPA2836) Typ value From: TBD To: -120 dB	3
• Changed the Common-mode rejection ratio Min value From: 94 dB To: 91 dB	4
• Added GAIN SETTING RESISTORS (OPA836IRUN ONLY)	5
• Changed the Quiescent operating current ($T_A = 25^\circ\text{C}$) Min value From: 0.8 mA To: 0.7 mA	5
• Changed the Power supply rejection ($\pm\text{PSRR}$) Min value From: 95 dB To: 91 dB	5
• Changed the Powerdown pin bias current CONDITIONS From: $\overline{\text{PD}} = 0.7\text{V}$ To: $\overline{\text{PD}} = 0.5\text{V}$	5
• Changed the Powerdown quiescent current CONDITIONS From: $\overline{\text{PD}} = 0.7\text{V}$ To: $\overline{\text{PD}} = 0.5\text{V}$	5
• Changed - Channel to channel crosstalk (OPA2836) Typ value From: TBD To: -120 dB	6
• Changed the Common-mode rejection ratio Min value From: 97 dB To: 94 dB	7
• Added GAIN SETTING RESISTORS (OPA836IRUN ONLY)	8
• Changed the Quiescent operating current ($T_A = 25^\circ\text{C}$) Min value From: 0.9 mA To: 0.8 mA	8
• Changed the Power supply rejection ($\pm\text{PSRR}$) Min value From: 97 dB To: 94 dB	8
• Changed the Powerdown quiescent current CONDITIONS From: $\overline{\text{PD}} = 0.7\text{V}$ To: $\overline{\text{PD}} = 0.5\text{V}$	8
• Changed the Powerdown quiescent current CONDITIONS From: $\overline{\text{PD}} = 0.7\text{V}$ To: $\overline{\text{PD}} = 0.5\text{V}$	8
• Changed the OPA836 WQFN-10 (RUN) pinout image	9
• Added Figure Crosstalk vs Frequency	14
• Added Figure Crosstalk vs Frequency	20
• Added section Single Ended to Differential Amplifier	24

Changes from Revision C (September 2011) to Revision D	Page
• Removed Product Preview from OPA836IRUNT and OPA836IRUNR	2
• Changed Resistor Temperature Coefficient Typ value From: TBD To: <10	5
• Changed Quiescent operating current To: Quiescent operating current per amplifier	5
• Changed Resistor Temperature Coefficient Typ value From: TBD To: <10	8
• Changed Quiescent operating current To: Quiescent operating current per amplifier	8

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
OPA2836ID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	2836	Samples
OPA2836IDGS	ACTIVE	VSSOP	DGS	10	80	Green (RoHS & no Sb/Br)	CU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	2836	Samples
OPA2836IDGSR	ACTIVE	VSSOP	DGS	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	2836	Samples
OPA2836IDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	2836	Samples
OPA2836IRMCR	ACTIVE	UQFN	RMC	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	2836	Samples
OPA2836IRMCT	ACTIVE	UQFN	RMC	10	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	2836	Samples
OPA2836IRUNR	ACTIVE	QFN	RUN	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	2836	Samples
OPA2836IRUNT	ACTIVE	QFN	RUN	10	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	2836	Samples
OPA836IDBVR	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU	Level-1-260C-UNLIM	-40 to 125	QTL	Samples
OPA836IDBVT	ACTIVE	SOT-23	DBV	6	250	Green (RoHS & no Sb/Br)	CU	Level-1-260C-UNLIM	-40 to 125	QTL	Samples
OPA836IRUNR	ACTIVE	QFN	RUN	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	836	Samples
OPA836IRUNT	ACTIVE	QFN	RUN	10	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	836	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
OPA2836IDGSR	VSSOP	DGS	10	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
OPA2836IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
OPA2836IRMCR	UQFN	RMC	10	3000	180.0	9.5	2.3	2.3	1.1	2.0	8.0	Q2
OPA2836IRMCT	UQFN	RMC	10	250	180.0	9.5	2.3	2.3	1.1	2.0	8.0	Q2
OPA2836IRUNR	QFN	RUN	10	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
OPA2836IRUNT	QFN	RUN	10	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
OPA836IDBVR	SOT-23	DBV	6	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
OPA836IDBVT	SOT-23	DBV	6	250	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
OPA836IRUNR	QFN	RUN	10	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
OPA836IRUNT	QFN	RUN	10	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
OPA2836IDGSR	VSSOP	DGS	10	2500	366.0	364.0	50.0
OPA2836IDR	SOIC	D	8	2500	340.5	338.1	20.6
OPA2836IRMCR	UQFN	RMC	10	3000	205.0	200.0	30.0
OPA2836IRMCT	UQFN	RMC	10	250	205.0	200.0	30.0
OPA2836IRUNR	QFN	RUN	10	3000	210.0	185.0	35.0
OPA2836IRUNT	QFN	RUN	10	250	210.0	185.0	35.0
OPA836IDBVR	SOT-23	DBV	6	3000	180.0	180.0	18.0
OPA836IDBVT	SOT-23	DBV	6	250	180.0	180.0	18.0
OPA836IRUNR	QFN	RUN	10	3000	210.0	185.0	35.0
OPA836IRUNT	QFN	RUN	10	250	210.0	185.0	35.0

MECHANICAL DATA

DBV (R-PDSO-G6)

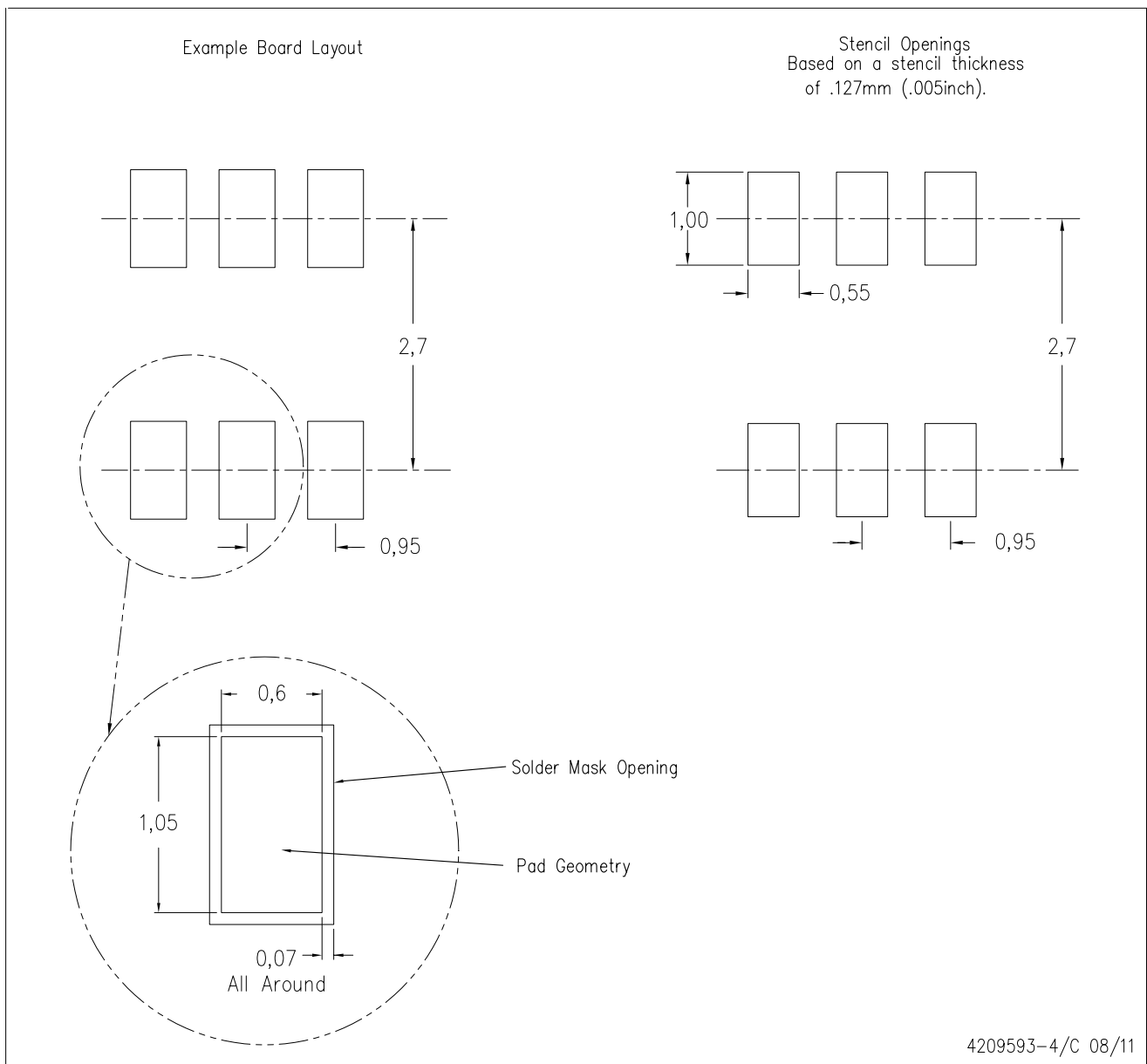
PLASTIC SMALL-OUTLINE PACKAGE



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
 - D. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
- Falls within JEDEC MO-178 Variation AB, except minimum lead width.

DBV (R-PDSO-G6)

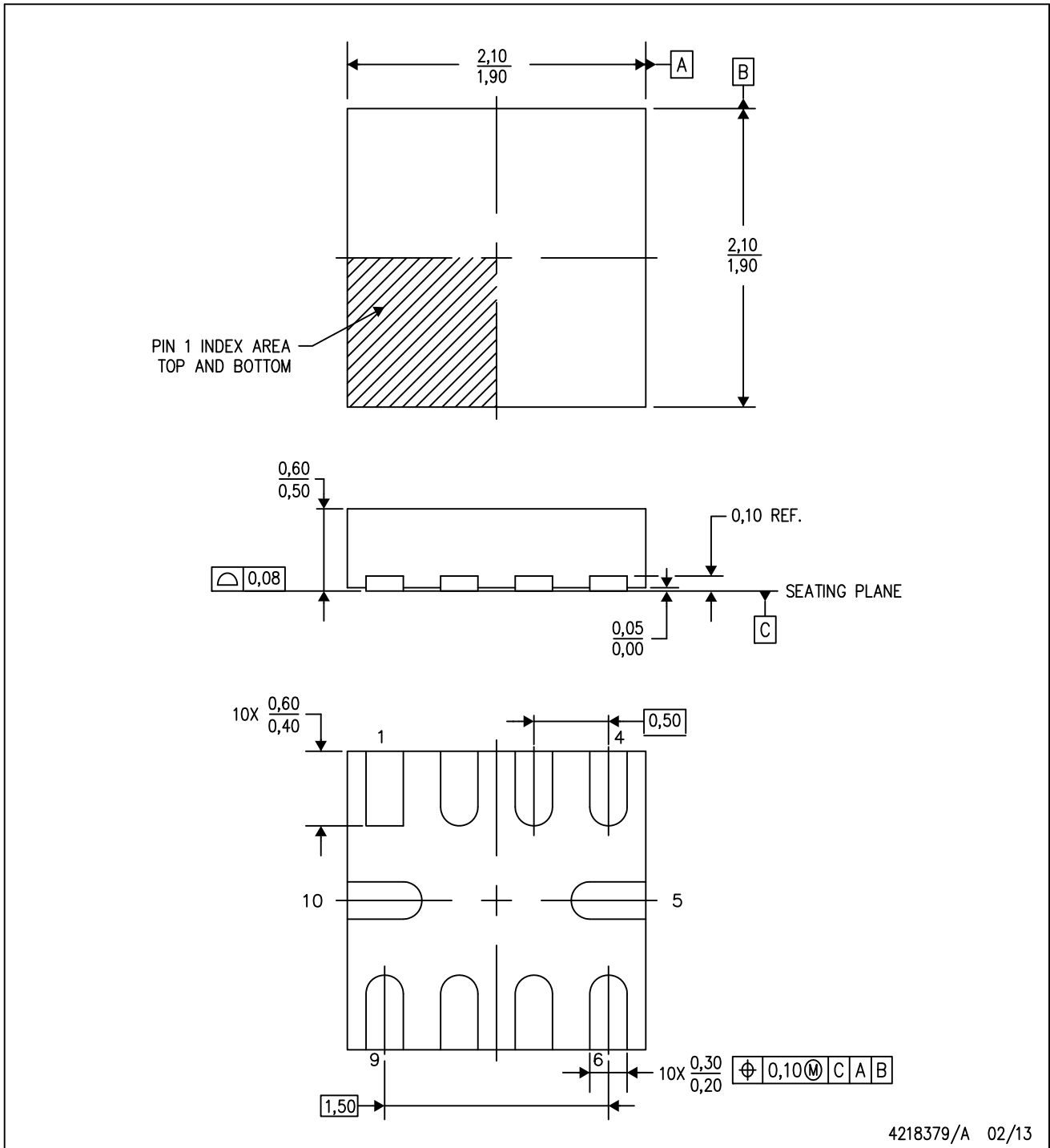
PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
 - D. Publication IPC-7351 is recommended for alternate designs.
 - E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.

RMC (S-PUQFN-N10)

PLASTIC QUAD FLATPACK NO-LEAD

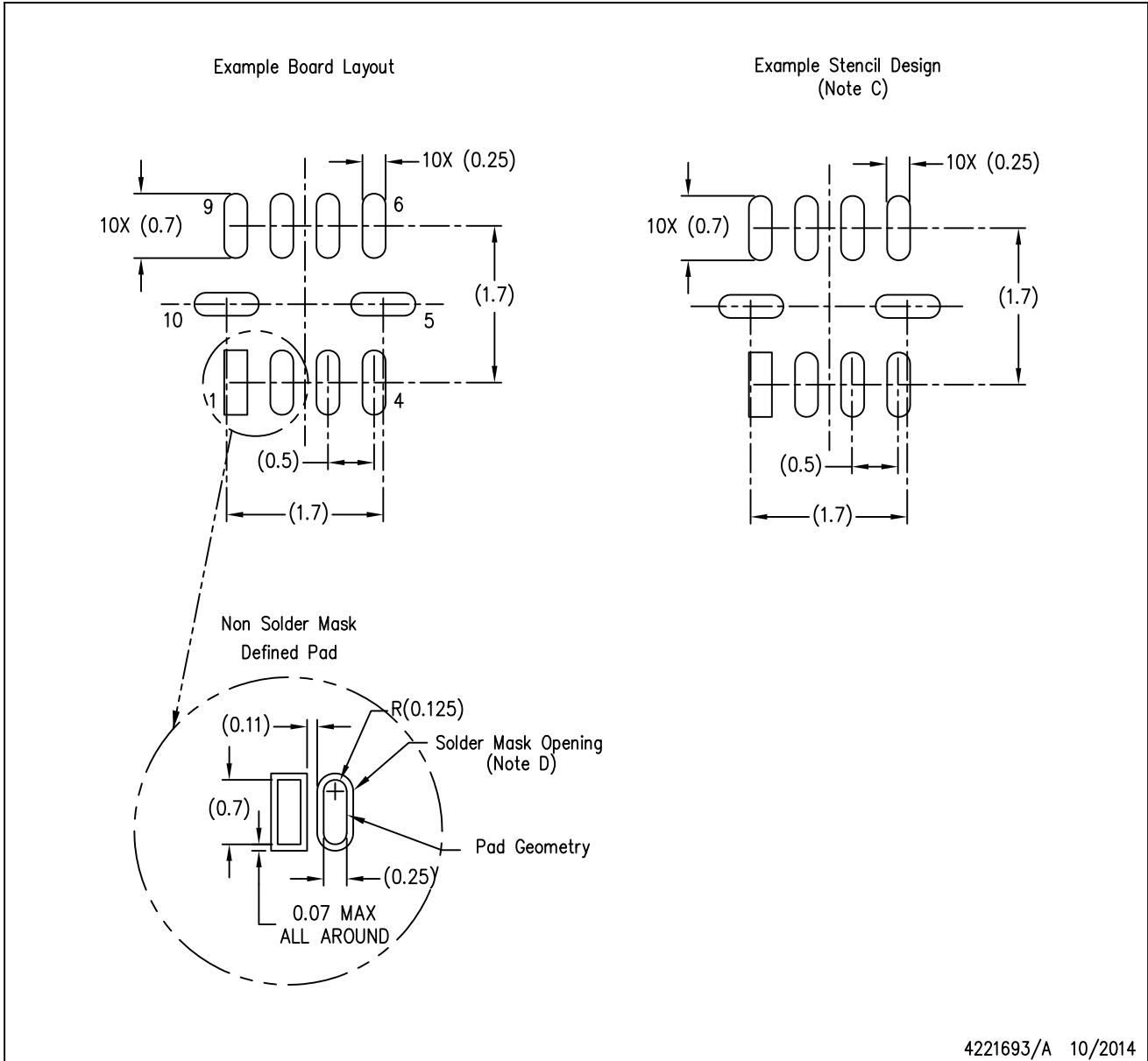


4218379/A 02/13

- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - B. This drawing is subject to change without notice.
 - C. Quad Flatpack, No-Leads (QFN) package configuration.

RMC (S-PUQFN-N10)

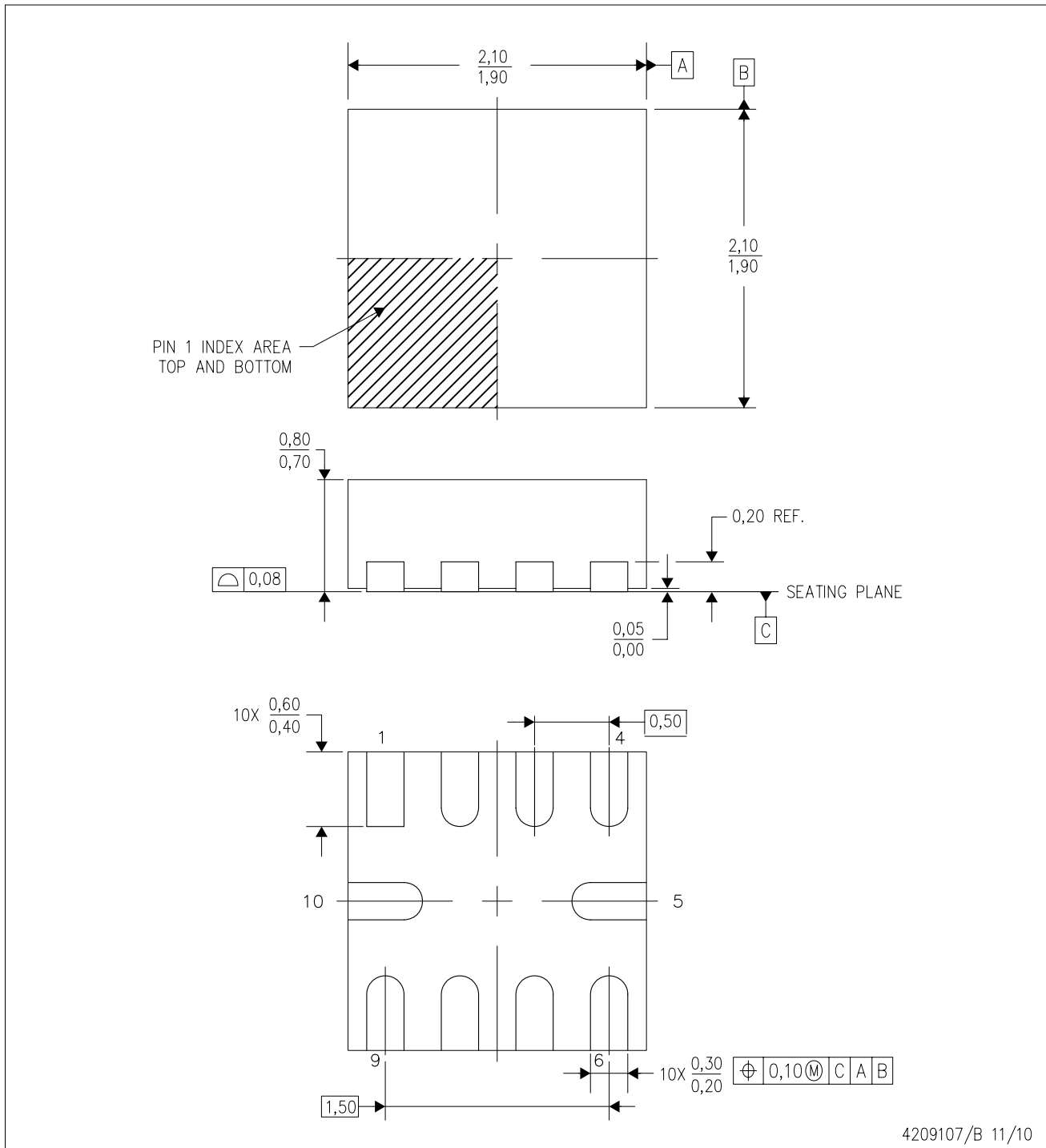
PLASTIC QUAD FLATPACK NO-LEAD



- NOTES:
- A. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only.
 - B. This drawing is subject to change without notice.
 - C. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
 - D. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.

RUN (S-PWQFN-N10)

PLASTIC QUAD FLATPACK NO-LEAD

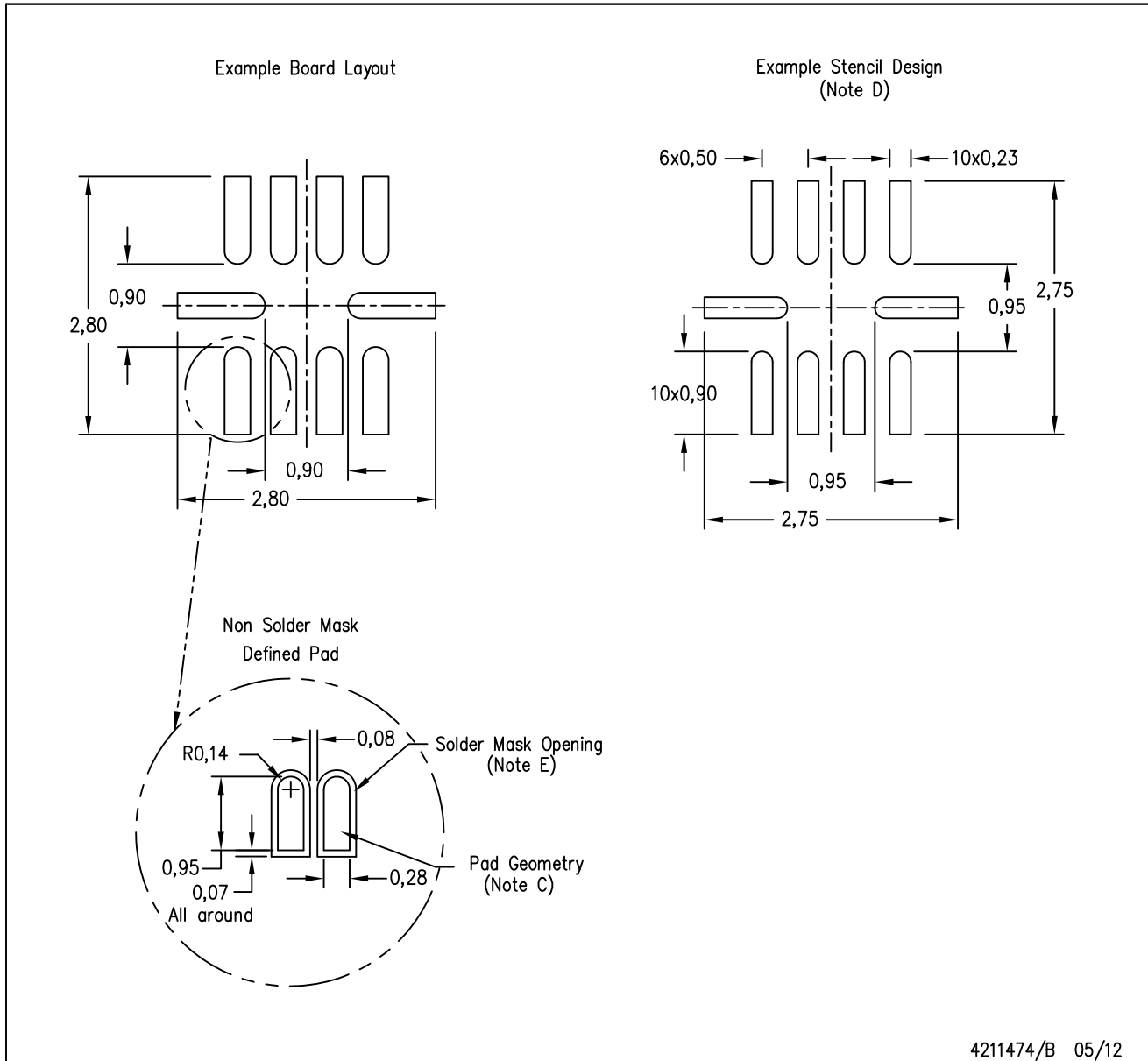


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- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - B. This drawing is subject to change without notice.
 - C. Quad Flatpack, No-Leads (QFN) package configuration.

RUN (S-PWQFN-N10)

PLASTIC QUAD FLATPACK NO-LEAD



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate designs.
 - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
 - E. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.

D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters).
 B. This drawing is subject to change without notice.
 C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
 D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
 E. Reference JEDEC MS-012 variation AA.

D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate designs.
 - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

DGS (S-PDSO-G10)

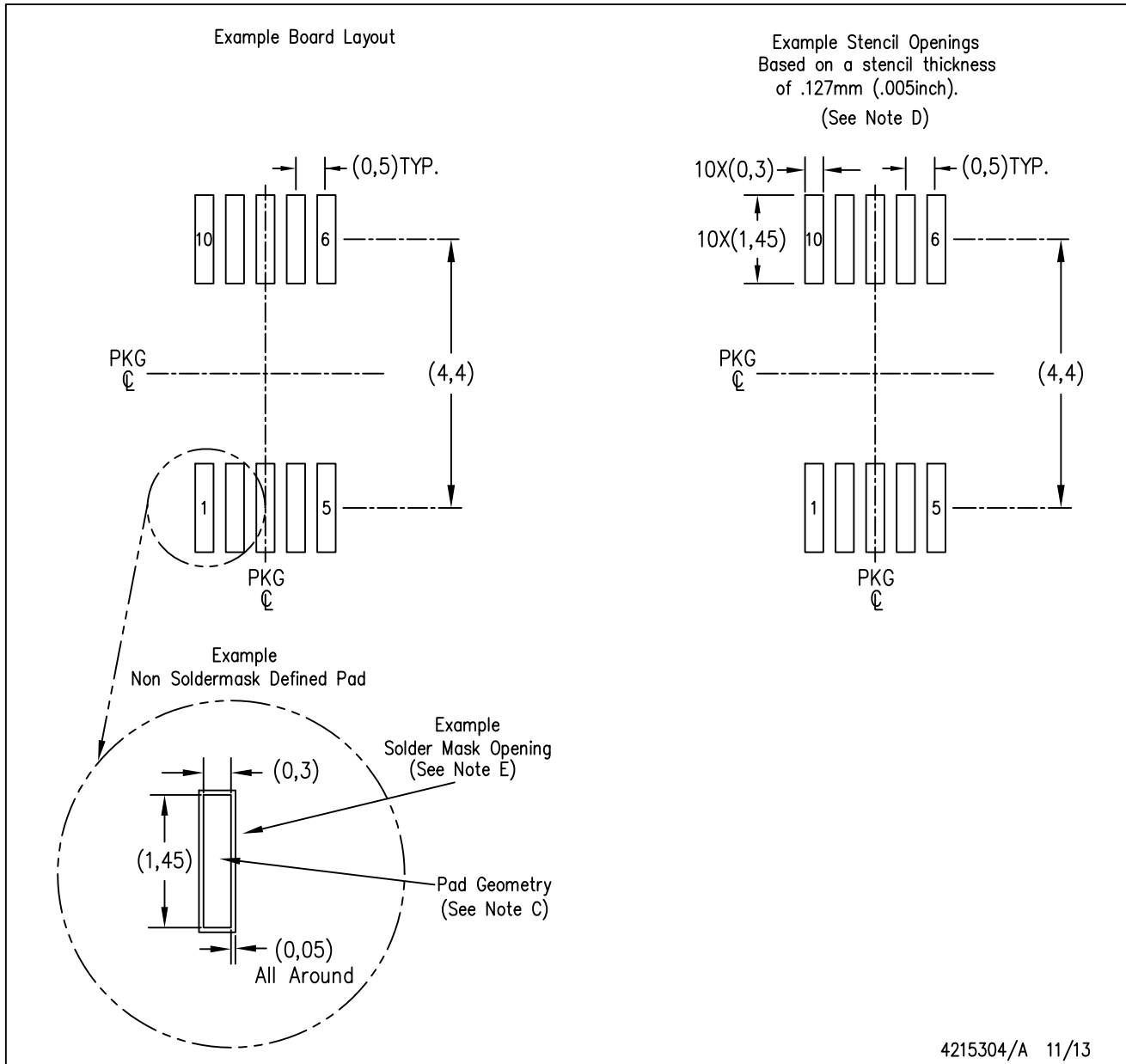
PLASTIC SMALL-OUTLINE PACKAGE



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion.
 - D. Falls within JEDEC MO-187 variation BA.

DGS (S-PDSO-G10)

PLASTIC SMALL OUTLINE PACKAGE



- NOTES:
- All linear dimensions are in millimeters.
 - This drawing is subject to change without notice.
 - Publication IPC-7351 is recommended for alternate designs.
 - Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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